

INA597 高精度、高带宽 e-trim™ 差分放大器

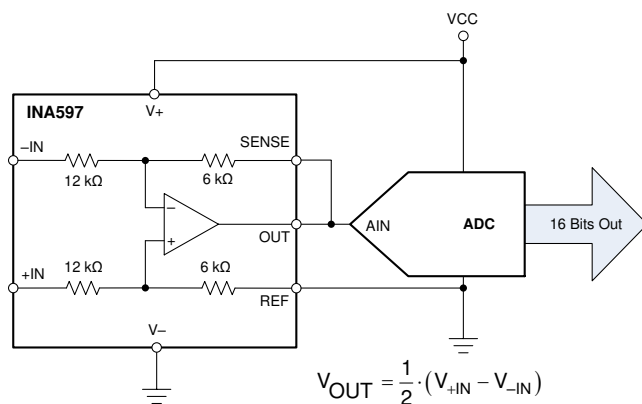
1 特性

- 低失调电压：200μV（最大值）
- 低失调电压漂移：±5μV/°C（最大值）
- 低噪声：1kHz 时为 18nV/√Hz
- 低增益误差：±0.03%（最大值）
- 高共模抑制：88dB（最小值）
- 高带宽：2MHz GBW
- 低静态电流：每个放大器 1.1mA
- 高压摆率：18V/μs
- 高容性负载驱动能力：500pF
- 宽电源电压范围：
 - 单电源：4.5V 至 36V
 - 双电源：±2.25V 至 ±18V
- 额定温度范围：
 - 40°C 至 +125°C
- 8 引脚 VSSOP 封装

2 应用

- 数据采集 (DAQ)
- 用于资产跟踪的传感器模块和标签
- 流量变送器
- 光学模块
- 电源模块
- 交流驱动器位置反馈
- 伺服驱动器位置反馈
- 电压调节模块

差分输入数据采集



3 说明

INA597 是一款低功耗、高带宽差分放大器，适用于成本敏感型应用。INA597 由精密运算放大器和精密电阻器网络组成。电阻器的出色跟踪性能在工作温度范围内保持增益精度和共模抑制。INA597 拥有独特特性，如低失调电压（最大值 200μV）、低温漂（最大值 5μV/°C）、高压摆率 (18V/μs) 和高达 500pF 的高容性负载驱动等，这些特性使其成为稳健的高性能差分放大器，适用于高电压工业应用。

内部运算放大器的共模范围可扩展至负电源，从而使该器件能够在单电源应用中运行。该器件采用单电源（4.5V 至 36V）或双电源（±2.25V 至 ±18V）运行。

差分放大器是许多常用电路的基础。INA597 提供此电路功能，而无需使用昂贵的精密电阻器网络。

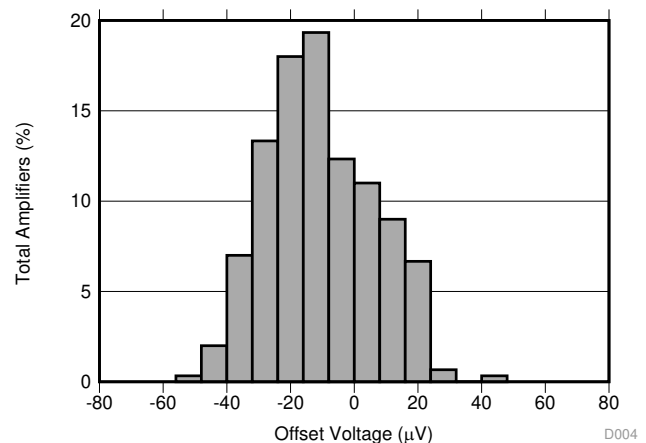
INA597 采用 8 引脚 VSSOP 表面贴装封装，额定工业温度范围为 -40°C 至 +125°C。

器件信息⁽¹⁾

器件型号	封装	封装尺寸（标称值）
INA597	VSSOP (8)	3.00mm × 3.00mm

(1) 如需了解所有可用封装，请参阅数据表末尾的封装选项附录。

失调电压的典型分布 (RTO)
G = 1/2, V_S = ±18V



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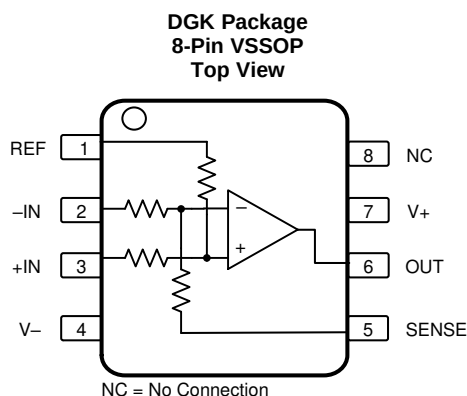
4 修订历史记录

日期	修订版本	说明
8 月2019 年	*	初始发行版。

5 Device Comparison Table

DEVICE	DESCRIPTION	GAIN EQUATION
INA597	Cost-Effective, Wide-Bandwidth e-trim™ Difference Amplifier	$G = 0.5 \text{ V/V or } 2 \text{ V/V}$
INA592	High-Precision, Wide-Bandwidth e-trim™ Difference Amplifier	$G = 0.5 \text{ V/V or } 2 \text{ V/V}$
INA159	$G = 0.2 \text{ V}$ Differential Amplifier for $\pm 10\text{-V}$ to 3-V and 5-V Conversion	$G = 0.2 \text{ V/V}$
INA137	Audio Differential Line Receiver $\pm 6 \text{ dB}$ ($G = 1/2$ or 2)	$G = 0.5 \text{ V/V or } 2 \text{ V/V}$
INA132	Low Power, Single-Supply Difference Amplifier	$G = 1 \text{ V/V}$
INA819	$35\text{-}\mu\text{V}$ Offset, $0.4 \mu\text{V}/^\circ\text{C}$ V_{OS} Drift, $8\text{-nV}/\sqrt{\text{Hz}}$ Noise, Low-Power, Precision Instrumentation Amplifier	$G = 1 + 50 \text{ k}\Omega / R_G$
INA821	$35\text{-}\mu\text{V}$ Offset, $0.4 \mu\text{V}/^\circ\text{C}$ V_{OS} Drift, $7\text{-nV}/\sqrt{\text{Hz}}$ Noise, High-Bandwidth, Precision Instrumentation Amplifier	$G = 1 + 49.4 \text{ k}\Omega / R_G$
INA333	$25\text{-}\mu\text{V}$ V_{OS} , $0.1 \mu\text{V}/^\circ\text{C}$ V_{OS} Drift, 1.8-V to 5-V , RRO, $50\text{-}\mu\text{A}$ I_Q , Chopper-Stabilized INA	$G = 1 + 100 \text{ k}\Omega / R_G$
PGA280	20-mV to $\pm 10\text{-V}$ Programmable Gain IA With 3-V or 5-V Differential Output; Analog Supply up to $\pm 18 \text{ V}$	Digital programmable
PGA112	Precision Programmable Gain Op Amp With SPI	Digital programmable

6 Pin Configuration and Functions



Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
+IN	3	I	12-kΩ resistor to noninverting pin of op amp. Used as positive input in $G = \frac{1}{2}$ configuration. Used as reference pin in $G = 2$ configuration.
-IN	2	I	12 kΩ resistor to inverting pin of op amp. Used as negative input in $G = \frac{1}{2}$ configuration. Connect to output in $G = 2$ configuration.
NC	8	—	No internal connection (can be left floating)
OUT	6	O	Output
REF	1	I	6-kΩ resistor to noninverting pin of op amp. Used as reference pin in $G = \frac{1}{2}$ configuration. Used as positive input in $G = 2$ configuration.
SENSE	5	I	6-kΩ resistor to inverting pin of op amp. Connect to output in $G = \frac{1}{2}$ configuration. Used as negative input in $G = 2$ configuration.
V+	7	—	Positive (highest) power supply
V-	4	—	Negative (lowest) power supply

7 Specifications

7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V _S	Supply voltage, V _S = (V+) – (V–)		36	V
V _{IN}	Input voltage	3(V–) – 0.3	3(V+)	V
I _S	Output short circuit (to ground)	Continuous		
T _A	Operating temperature	–55	125	°C
T _J	Junction temperature	–55	125	°C
T _{stg}	Storage temperature		150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

7.2 ESD Ratings

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±500	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1000	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	NOM	MAX	UNIT
V _S	Supply voltage, V _S = (V+) – (V–)	Single Supply	4.5		36	V
		Dual Supply	±2.25		±18	V
T _A	Specified temperature		–40		125	°C

7.4 Thermal Information

THERMAL METRIC ⁽¹⁾		INA597	UNIT
		DGK (VSSOP)	
		8 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	158	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	48.6	°C/W
R _{θJB}	Junction-to-board thermal resistance	78.7	°C/W
ψ _{JT}	Junction-to-top characterization parameter	3.9	°C/W
ψ _{JB}	Junction-to-board characterization parameter	77.3	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	°C/W

- (1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

7.5 Electrical Characteristics: G = 1/2

at $V_S = \pm 2.25 \text{ V}$ to $\pm 18 \text{ V}$, $T_A = 25^\circ\text{C}$, $V_{CM} = V_{OUT} = V_S / 2$, $R_L = 10 \text{ k}\Omega$ connected to ground, and REF pin connected to ground (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
OFFSET VOLTAGE (RTO) ⁽¹⁾							
V _{OS}	Input offset voltage	G = 1/2, RTO, T _A = 25°C, V _S = ±2.25 V to ±3 V, V _{CM} = −3 V			±14	±200	μV
		G = 1/2, RTO, T _A = 25°C, V _S = ±3 V to ±18 V, V _{CM} = V _S / 2			±14	±200	μV
dV _{OS} /dT	Input offset voltage drift				±0.7	±5.0	μV/°C
PSRR	Power-supply rejection ratio	V _S = ±3 V to ±18 V			±0.5	±5	μV/V
INPUT VOLTAGE							
V _{CM}	Common-mode voltage	V _{OUT} = 0 V		3(V−) − 0.3		3(V+)	V
CMRR	Common-mode rejection ratio	RTO, 3 [(V−) − 0.1 V]] ≤ V _{CM} ≤ 3 [(V+) − 3 V]	T _A = 25°C	88	100		dB
			T _A = −40°C to +125°C	82	90		dB
		RTO, 3 [(V+) - 1.5 V]] ≤ V _{CM} ≤ 3 [(V+)]	T _A = 25°C	88	100		dB
			T _A = −40°C to +125°C	72	90		dB
INPUT IMPEDANCE ⁽²⁾							
GAIN							
G	Initial				1/2		V/V
GE	Gain error	V _{OUT} = −10 V to +10 V, V _S = ±15 V			±0.01%	±0.03%	
	Gain error drift ⁽³⁾				±0.2	±0.5	ppm/°C
	Gain nonlinearity	V _{OUT} = −10 V to +10 V, V _S = ±15 V			1		ppm
OUTPUT							
V _O	Voltage output swing from rail	Positive rail, R _L = 10 kΩ to ground			170	220	mV
		Negative rail, R _L = 10 kΩ to ground			190	220	mV
I _{SC}	Short-circuit current				±65		mA
C _{LOAD}	Capacitive load (stable operation)	See 图 49					
NOISE							
V _n	Output voltage noise	f = 0.1 Hz to 10 Hz, RTO			3		μVpp
	Output voltage noise density	f = 1 kHz, RTO			18		nV/√Hz
FREQUENCY RESPONSE							
GBW	Small signal bandwidth	Amplitude = −3 dB			2.0		MHz
SR	Slew rate				18		V/μs
t _S	Settling time	To 0.1%	V _{OUT} = 10-V step		1		μs
		To 0.01%			1.3		μs
THD+N	Total harmonic distortion + noise	f = 1 kHz, V _{OUT} = 2.8 V _{RMS}			0.00038 %		
	Noise floor, RTO	80-kHz bandwidth, V _{OUT} = 3.5 V _{RMS}			−116		dB
t _{DR}	Overload recovery time				200		ns
POWER SUPPLY							
I _Q	Quiescent current	I _{OUT} = 0 mA	T _A = 25°C		1.1	1.2	mA
			T _A = −40°C to +125°C			1.5	mA

(1) Includes effects of input bias and offset currents of amplifier.

(2) Resistors are ratio matched but have $\pm 20\%$ absolute value.

(3) Specified by wafer test to 95% confidence level.

7.6 Electrical Characteristics: G = 2

at $V_S = \pm 2.25\text{ V}$ to $\pm 18\text{ V}$, $T_A = 25^\circ\text{C}$, $V_{CM} = V_{OUT} = V_S / 2$, $R_L = 10\text{ k}\Omega$ connected to ground, and REF pin connected to ground (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
OFFSET VOLTAGE (RTO) ⁽¹⁾							
V _{OS}	Input offset voltage	G = 2, RTO, T _A = 25°C, V _S = ±2.25 V to ±3 V, V _{CM} = −1.5 V			±28	±400	μV
		G = 2, RTO, T _A = 25°C, V _S = ±3 V to ±18 V, V _{CM} = V _S / 2			±28	±400	μV
dV _{OS} /dT	Input offset voltage drift				±1.4	±10	μV/°C
PSRR	Power-supply rejection ratio	V _S = ±2.25 V to ±18 V			±1	±5	μV/V
INPUT VOLTAGE							
V _{CM}	Common-mode voltage	V _{OUT} = 0 V		1.5(V−) − 0.15		1.5(V+)	V
CMRR	Common-mode rejection ratio	RTO, 1.5 [(V−) − 0.1 V] ≤ V _{CM} ≤ 1.5 [(V+) − 3 V)]	T _A = 25°C	82	94		dB
			T _A = −40°C to +125°C	80	84		dB
		RTO, 1.5 [(V+) - 1.5 V] ≤ V _{CM} ≤ 1.5 [(V+)]	T _A = 25°C	82	94		dB
			T _A = −40°C to +125°C	65	84		dB
INPUT IMPEDANCE ⁽²⁾							
GAIN							
G	Initial				2		V/V
GE	Gain error	V _{OUT} = −10 V to +10 V, V _S = ±15 V			±0.01%	±0.03%	
	Gain error drift ⁽³⁾				±0.25	±0.5	ppm/°C
	Gain nonlinearity	V _{OUT} = −10 V to +10 V, V _S = ±15 V			1		ppm
OUTPUT							
V _O	Voltage output swing from rail	Positive rail, R _L = 10 kΩ to ground			130	180	mV
		Negative rail, R _L = 10 kΩ to ground			140	180	mV
I _{SC}	Short-circuit current				±65		mA
C _{LOAD}	Capacitive load (stable operation)	see 图 50					
NOISE							
V _n	Output voltage noise	f = 0.1 Hz to 10 Hz, RTO			6		μVpp
	Output voltage noise density	f = 1 kHz, RTO			36		nV/√Hz
FREQUENCY RESPONSE							
GBW	Small signal bandwidth	Amplitude = −3 dB			0.8		MHz
SR	Slew rate				18		V/μs
t _S	Settling time	To 0.1%	V _{OUT} = 10-V step		1.0		μs
		To 0.01%			1.7		μs
THD+N	Total harmonic distortion + noise	f = 1 kHz, V _{OUT} = 2.8 V _{RMS}			0.00066 %		
	Noise floor, RTO	80-kHz bandwidth, V _{OUT} = 3.5 V _{RMS}			−110		dB
t _{DR}	Overload recovery time				200		ns
POWER SUPPLY							
I _Q	Quiescent current	I _{OUT} = 0 mA	T _A = 25°C		1.1	1.2	mA
			T _A = −40°C to +125°C			1.5	mA

(1) Includes effects of input bias and offset currents of amplifier.

(2) Resistors are ratio matched but have $\pm 20\%$ absolute value.

(3) Specified by wafer test to 95% confidence level.

7.7 Typical Characteristics: Table of Graphs

表 1. Table of Graphs

DESCRIPTION	FIGURE
Typical Distribution of Offset Voltage (RTO) $G = 1/2$, $V_S = \pm 2.25\text{ V}$	图 1
Typical Distribution of Offset Voltage (RTO) $G = 2$, $V_S = \pm 2.25\text{ V}$	图 2
Typical Distribution of Offset Voltage (RTO) $G = 1/2$, $V_S = \pm 18\text{ V}$	图 3
Typical Distribution of Offset Voltage (RTO) $G = 2$, $V_S = \pm 18\text{ V}$	图 4
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Input Bias Current vs Temperature $G = 1/2$ and $G = 2$	图 11
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Large Signal Step Response $G = 2$	图 46

Typical Characteristics: Table of Graphs (接下页)

表 1. Table of Graphs (接下页)

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THD+N vs Frequency $G = 1/2$	图 53
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Input Common-Mode Voltage vs Output Voltage $G = 1/2$, 36-V Supply	图 71
Input Common-Mode Voltage vs Output Voltage $G = 2$, 36-V Supply	图 72
Closed-Loop Output Impedance vs Frequency	图 73

7.8 Typical Characteristics

at $T_A = 25^\circ\text{C}$, $V_S = \pm 18\text{ V}$, $V_{CM} = V_{OUT} = V_S / 2$, $R_L = 10\text{ k}\Omega$, REF pin connected to ground, $G = 1/2$ (unless otherwise noted)

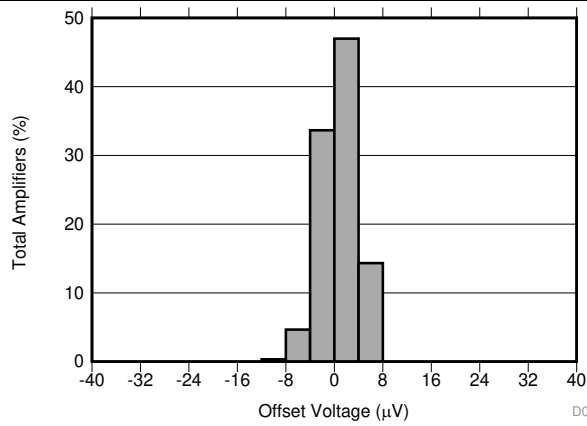


图 1. Typical Distribution of Offset Voltage (RTO)

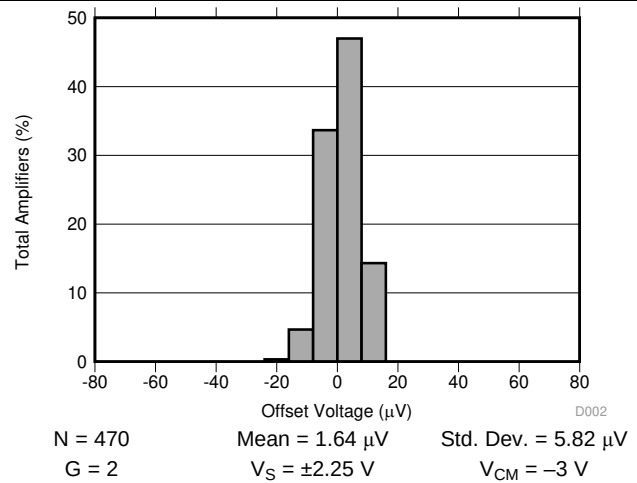


图 2. Typical Distribution of Offset Voltage (RTO)

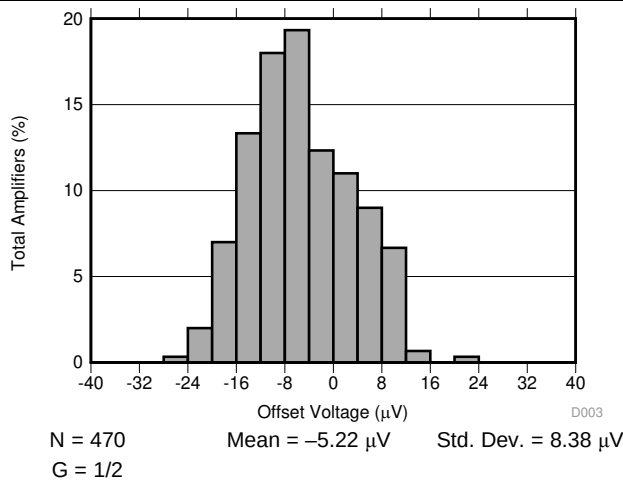


图 3. Typical Distribution of Offset Voltage (RTO)

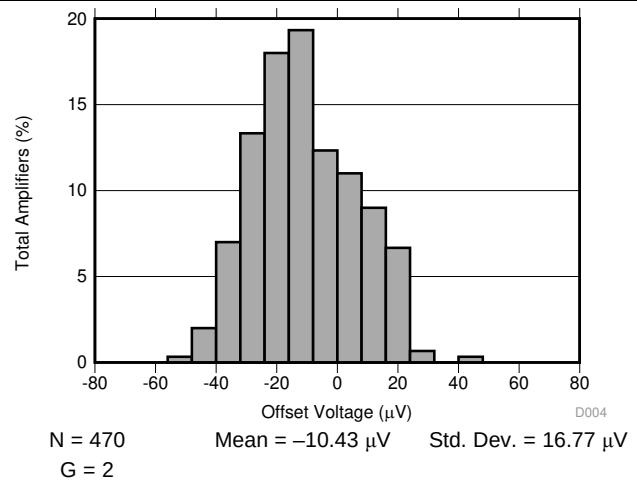


图 4. Typical Distribution of Offset Voltage (RTO)

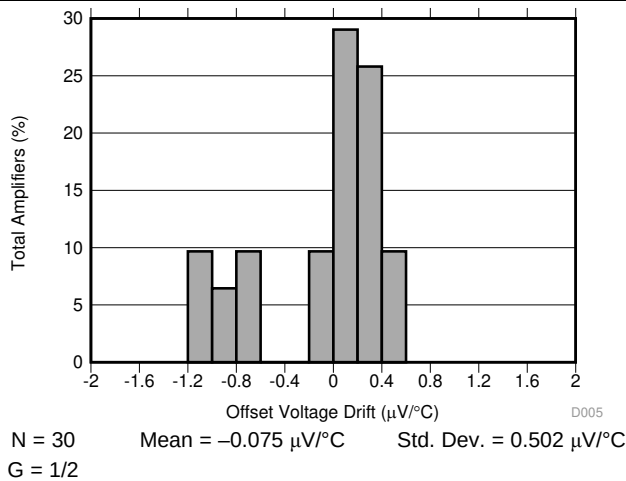


图 5. Typical Distribution of Offset Voltage Drift (RTO)

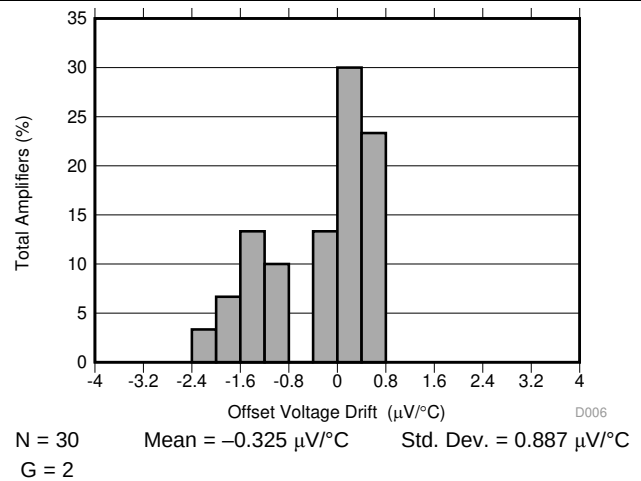
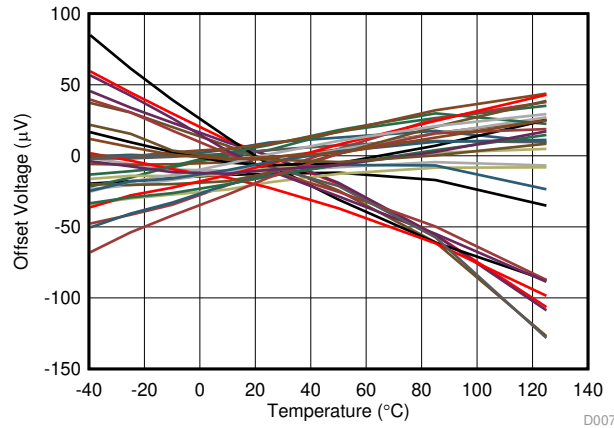


图 6. Typical Distribution of Offset Voltage Drift (RTO)

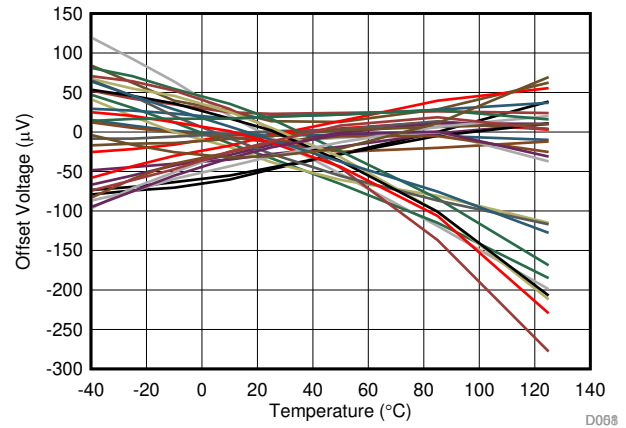
Typical Characteristics (接下页)

at $T_A = 25^\circ\text{C}$, $V_S = \pm 18\text{ V}$, $V_{CM} = V_{OUT} = V_S / 2$, $R_L = 10\text{ k}\Omega$, REF pin connected to ground, $G = 1/2$ (unless otherwise noted)



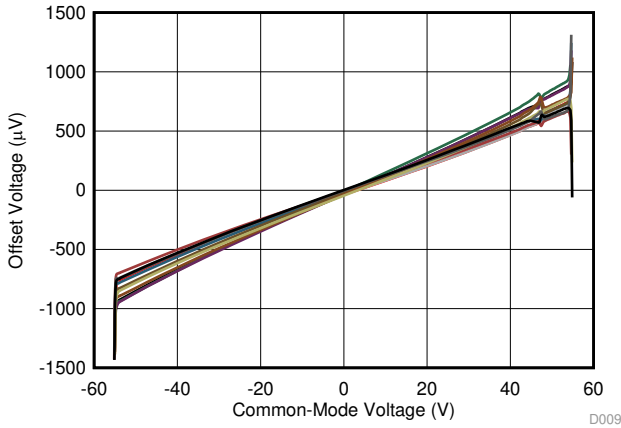
$G = 1/2$ 30 units

图 7. Output Offset Voltage vs Temperature



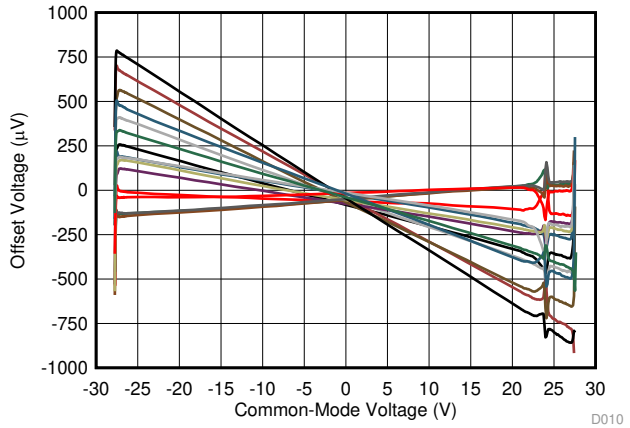
$G = 2$ 30 units

图 8. Output Offset Voltage vs Temperature



$G = 1/2$ 12 units

图 9. Offset Voltage vs Common-Mode Voltage



$G = 2$ 12 units

图 10. Offset Voltage vs Common-Mode Voltage

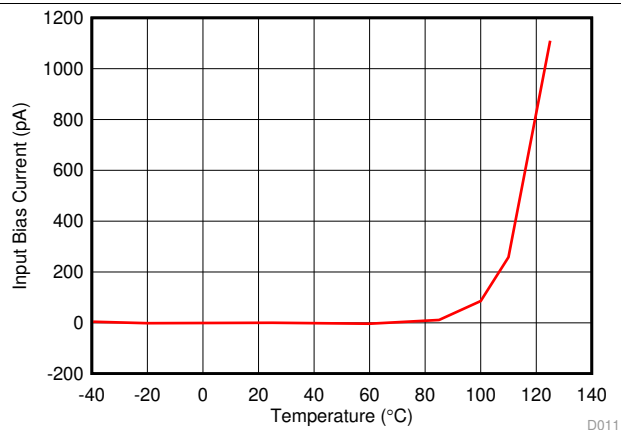


图 11. Input Bias Current vs Temperature

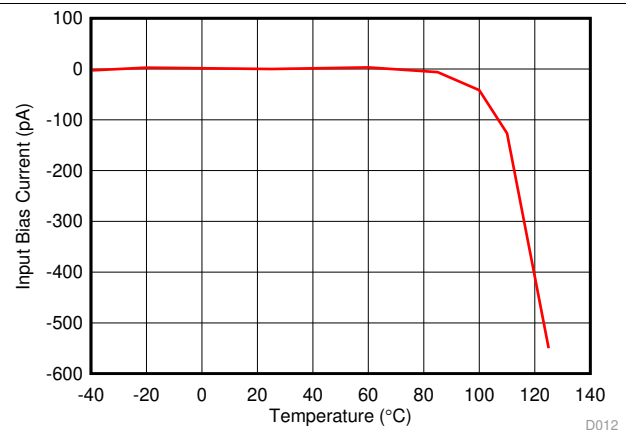
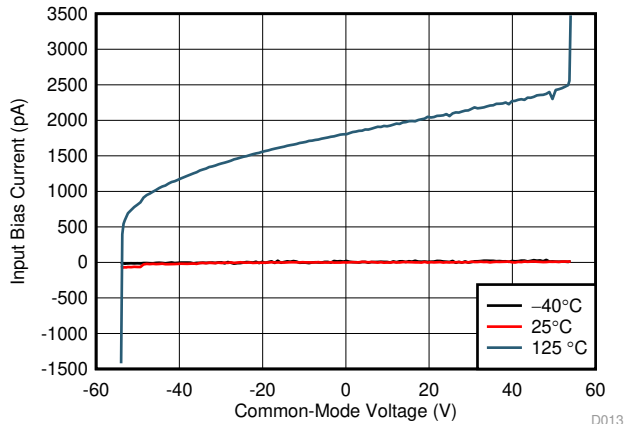


图 12. Input Offset Current vs Temperature

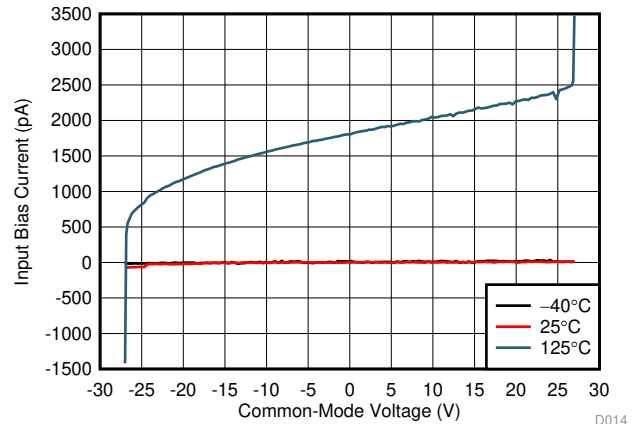
Typical Characteristics (接下页)

at $T_A = 25^\circ\text{C}$, $V_S = \pm 18\text{ V}$, $V_{CM} = V_{OUT} = V_S / 2$, $R_L = 10\text{ k}\Omega$, REF pin connected to ground, $G = 1/2$ (unless otherwise noted)



$G = 1/2$

图 13. Input Bias Current vs Common-Mode Voltage



$G = 2$

图 14. Input Bias Current vs Common-Mode Voltage

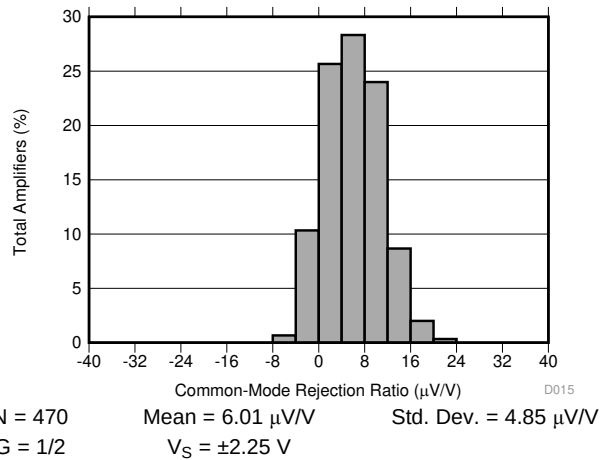


图 15. Typical CMRR Distribution

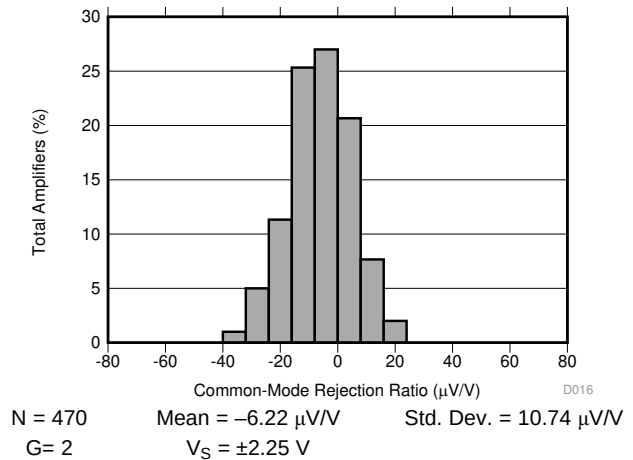


图 16. Typical CMRR Distribution ,

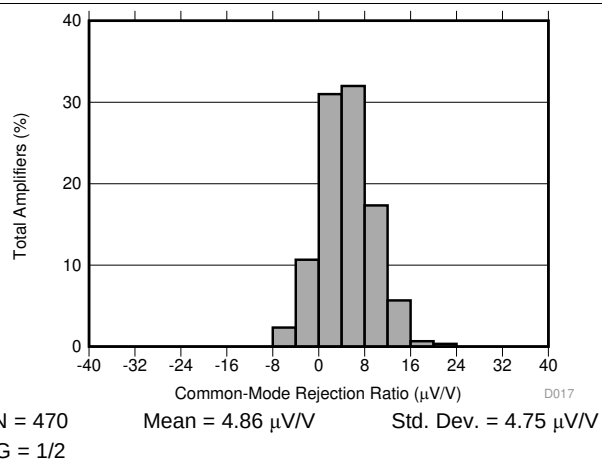


图 17. Typical CMRR Distribution

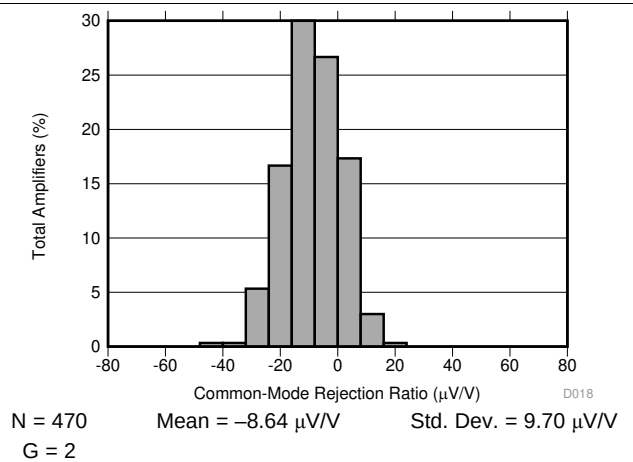


图 18. Typical CMRR Distribution

Typical Characteristics (接下页)

at $T_A = 25^\circ\text{C}$, $V_S = \pm 18\text{ V}$, $V_{CM} = V_{OUT} = V_S / 2$, $R_L = 10\text{ k}\Omega$, REF pin connected to ground, $G = 1/2$ (unless otherwise noted)

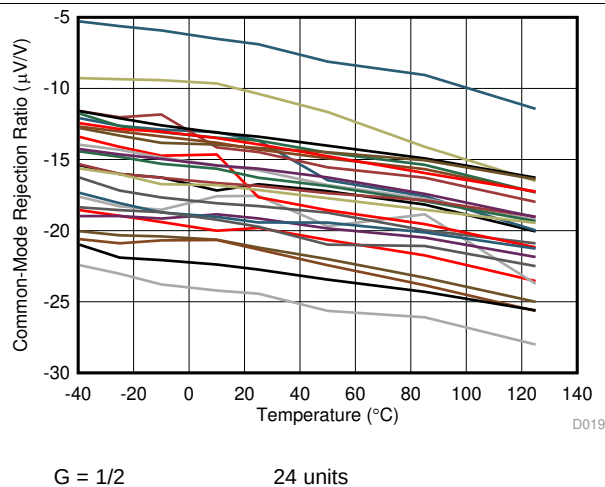


图 19. CMRR vs Temperature

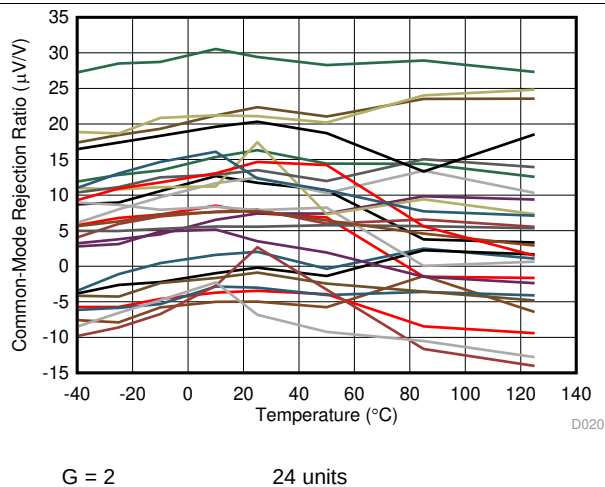


图 20. CMRR vs Temperature

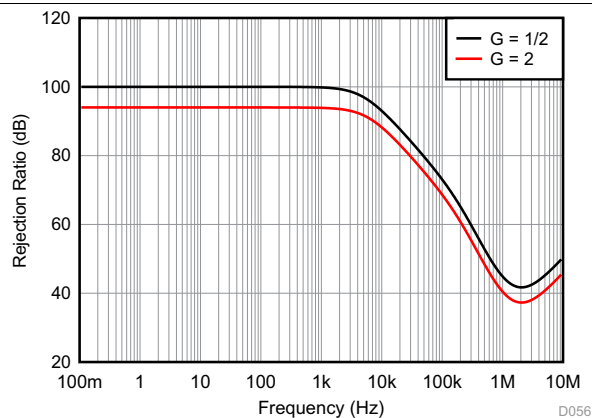


图 21. Common-Mode Rejection Ratio vs Frequency, Referred-to-Input

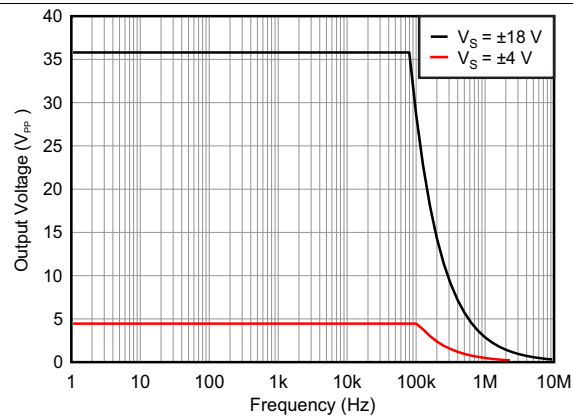


图 22. Maximum Output Voltage vs Frequency

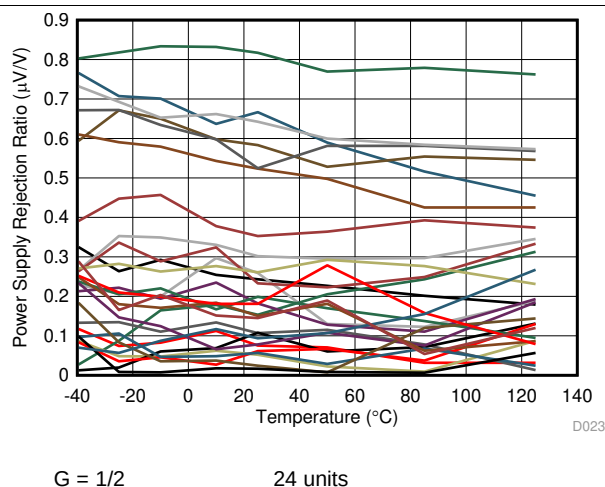


图 23. PSRR vs Temperature

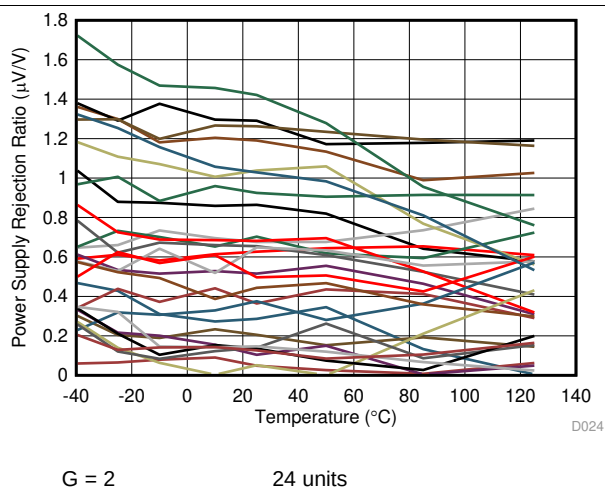


图 24. PSRR vs Temperature

Typical Characteristics (接下页)

at $T_A = 25^\circ\text{C}$, $V_S = \pm 18\text{ V}$, $V_{CM} = V_{OUT} = V_S / 2$, $R_L = 10\text{ k}\Omega$, REF pin connected to ground, $G = 1/2$ (unless otherwise noted)

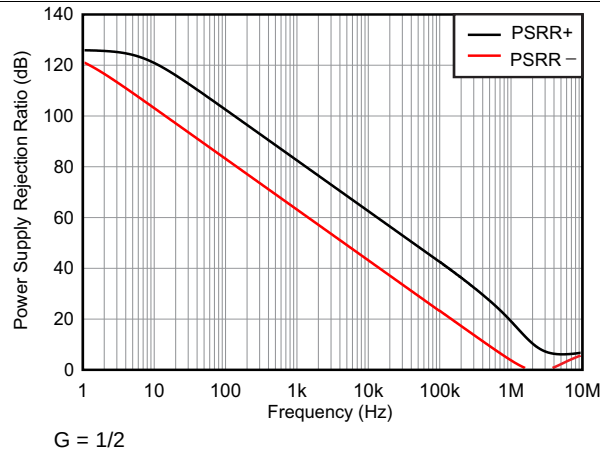


图 25. PSRR vs Frequency (RTI)

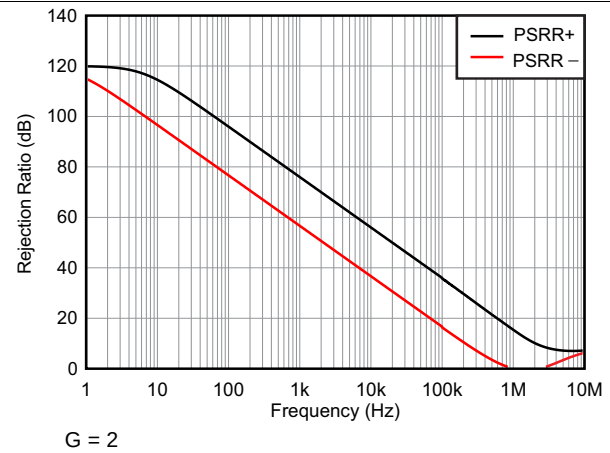


图 26. PSRR vs Frequency (RTI)

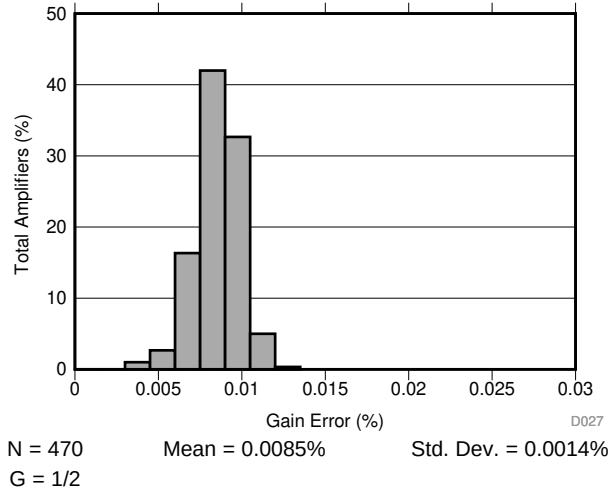


图 27. Typical Distribution of Gain Error

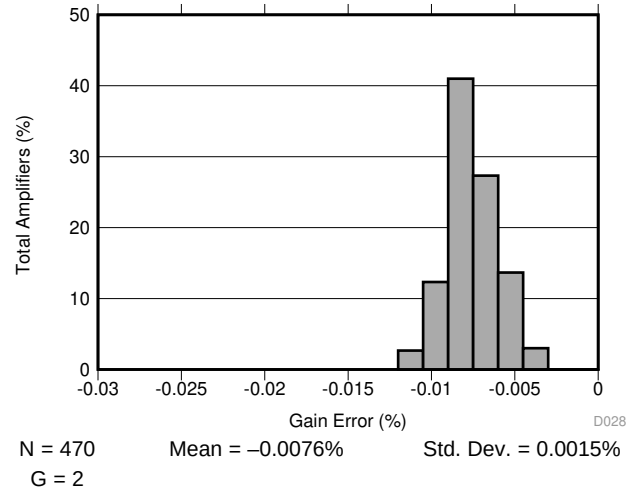


图 28. Typical Distribution of Gain Error

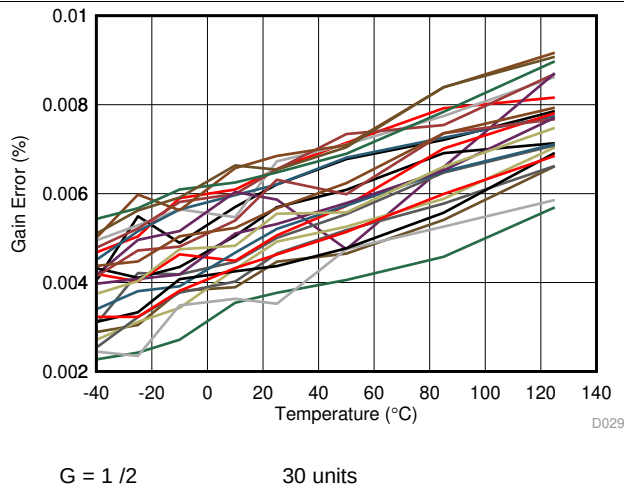


图 29. Gain Error vs Temperature

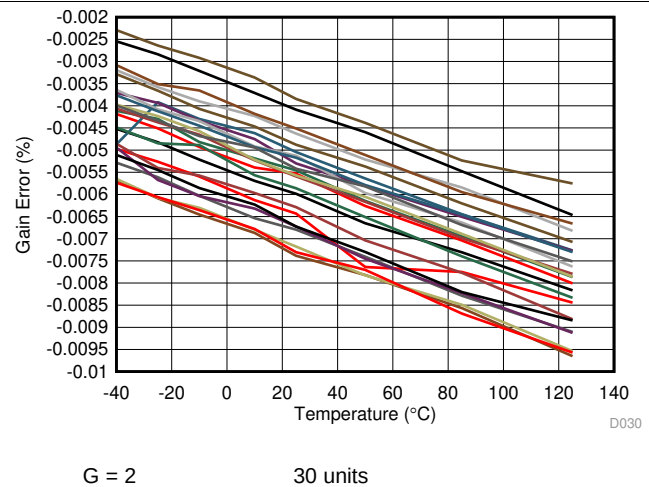


图 30. Gain Error vs Temperature

Typical Characteristics (接下页)

at $T_A = 25^\circ\text{C}$, $V_S = \pm 18\text{ V}$, $V_{CM} = V_{OUT} = V_S / 2$, $R_L = 10\text{ k}\Omega$, REF pin connected to ground, $G = 1/2$ (unless otherwise noted)

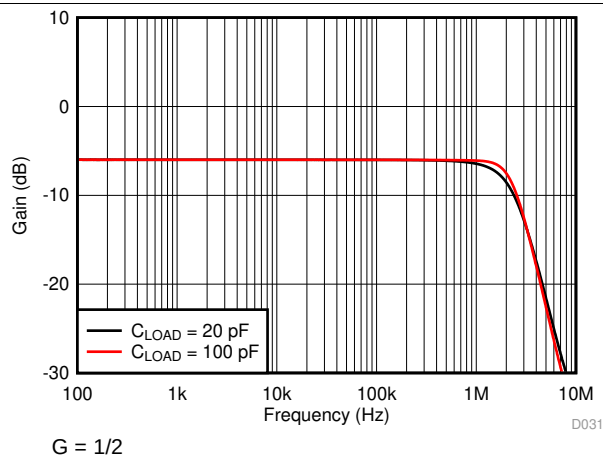


图 31. Closed-Loop Gain vs Frequency

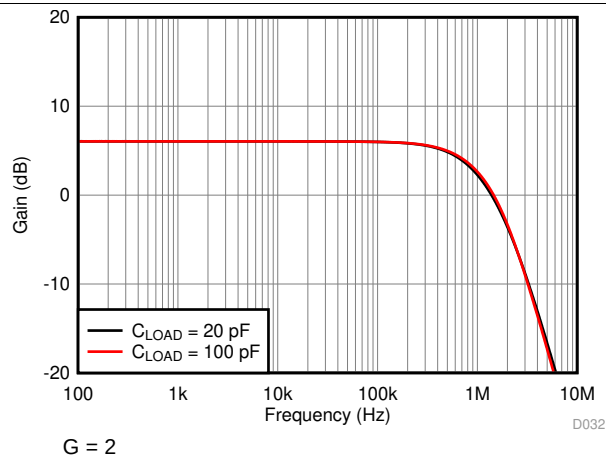


图 32. Closed-Loop Gain vs Frequency

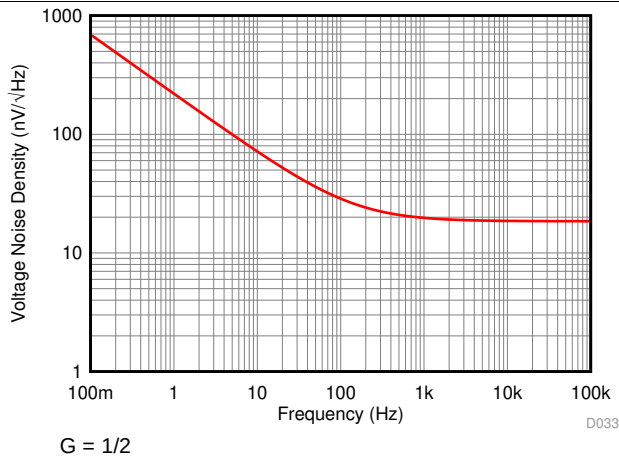


图 33. Voltage Noise Spectral Density vs Frequency (RTI)

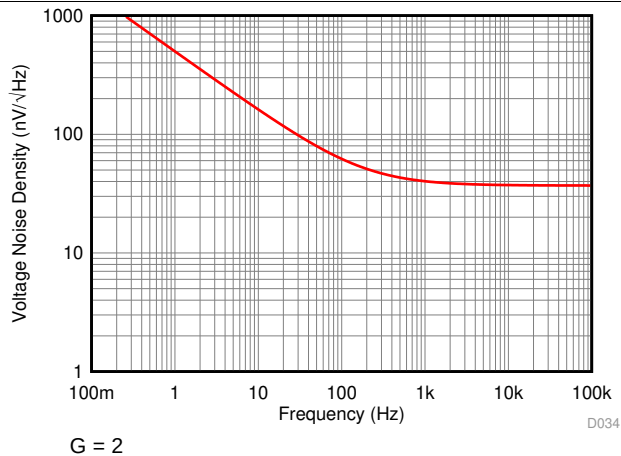


图 34. Voltage Noise Spectral Density vs Frequency (RTI)

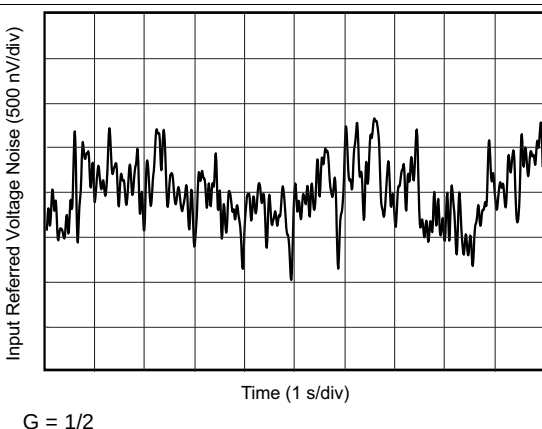


图 35. 0.1-Hz to 10-Hz RTI Voltage Noise

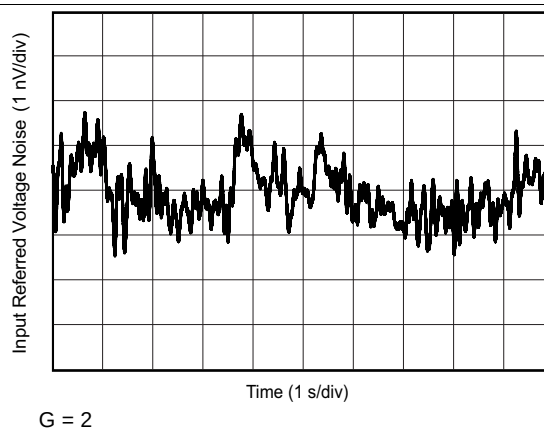
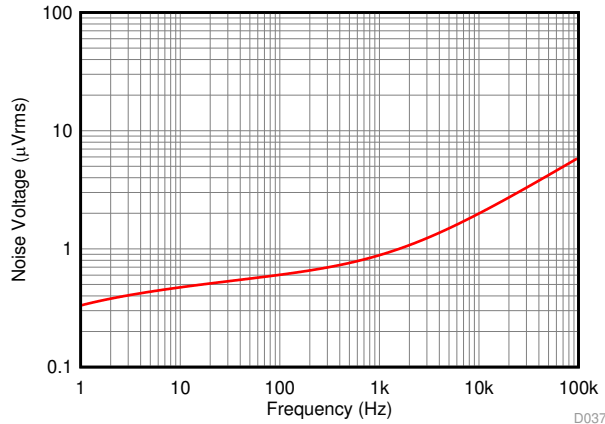


图 36. 0.1-Hz to 10-Hz RTI Voltage Noise

Typical Characteristics (接下页)

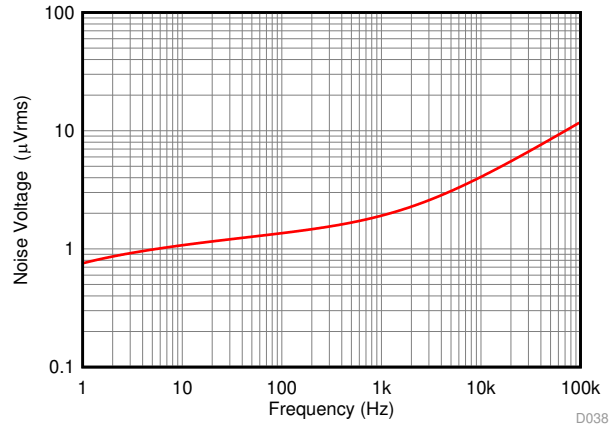
at $T_A = 25^\circ\text{C}$, $V_S = \pm 18\text{ V}$, $V_{CM} = V_{OUT} = V_S / 2$, $R_L = 10\text{ k}\Omega$, REF pin connected to ground, $G = 1/2$ (unless otherwise noted)



$G = 1/2$

D037

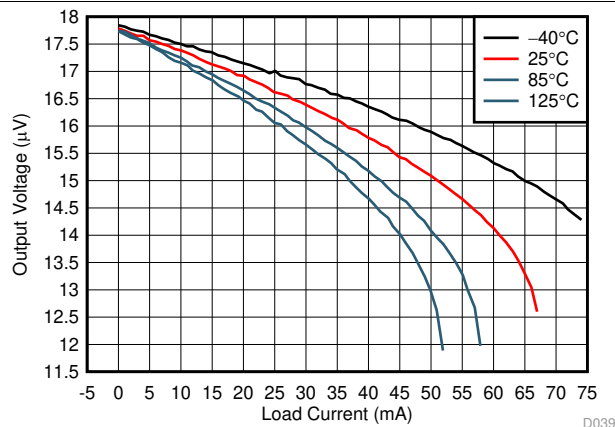
图 37. Integrated Output Voltage Noise vs Noise Bandwidth



$G = 2$

D038

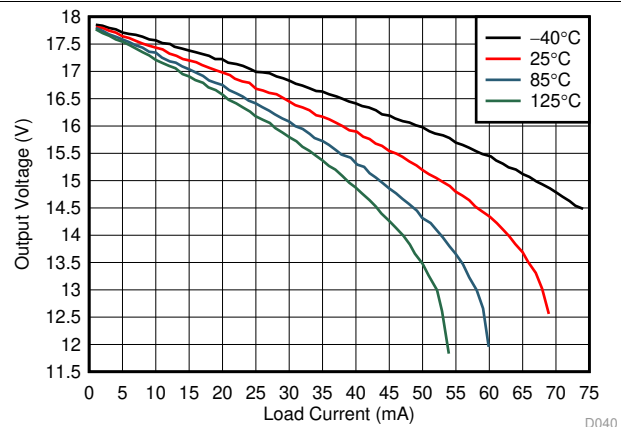
图 38. Integrated Output Voltage Noise vs Noise Bandwidth



$G = 1/2$

D039

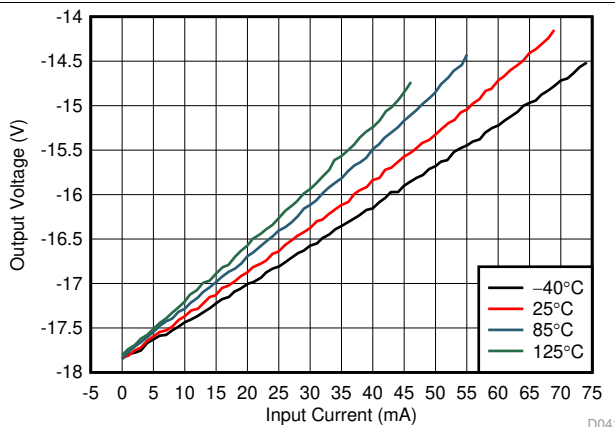
图 39. Positive Output Voltage vs Output Current (Sourcing)



$G = 2$

D040

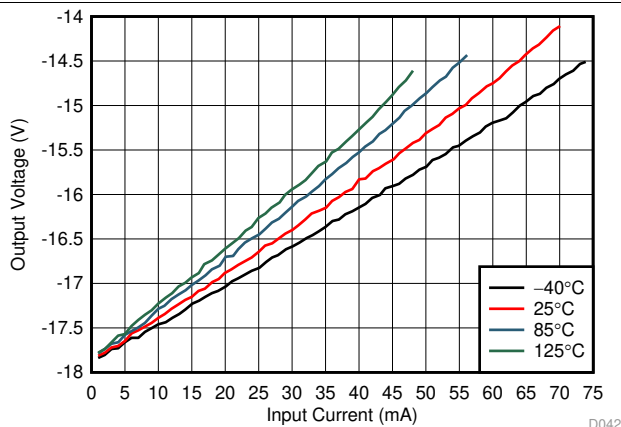
图 40. Positive Output Voltage vs Output Current (Sourcing)



$G = 1/2$

D041

图 41. Negative Output Voltage vs Output Current (Sinking)



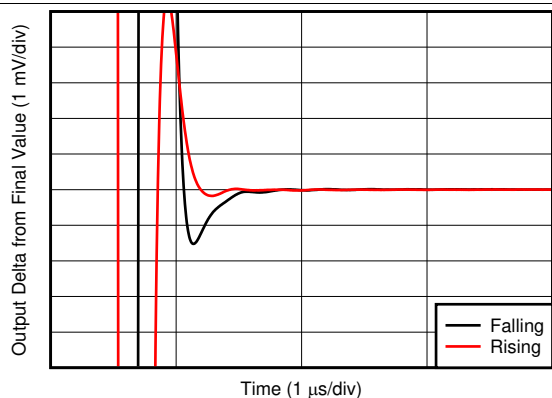
$G = 2$

D042

图 42. Negative Output Voltage vs Output Current (Sinking)

Typical Characteristics (接下页)

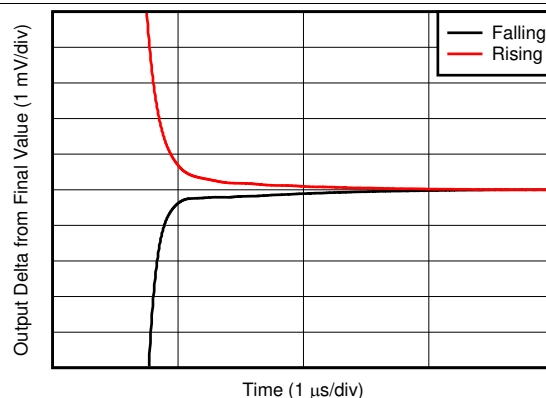
at $T_A = 25^\circ\text{C}$, $V_S = \pm 18\text{ V}$, $V_{CM} = V_{OUT} = V_S / 2$, $R_L = 10\text{ k}\Omega$, REF pin connected to ground, $G = 1/2$ (unless otherwise noted)



$G = 1/2$

D043

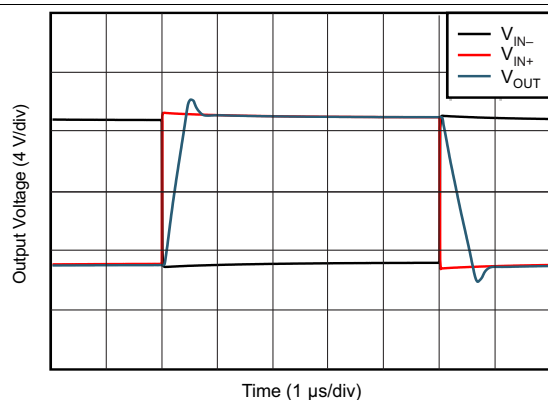
图 43. Settling Time



$G = 2$

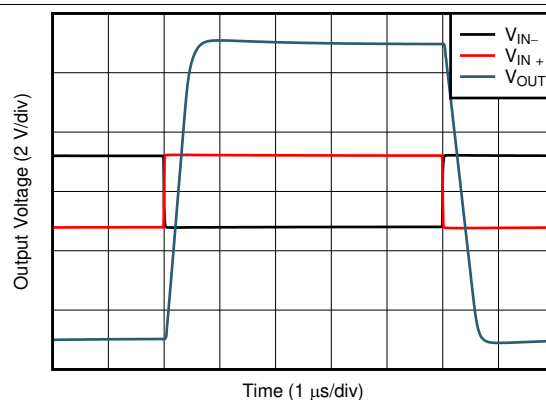
D044

图 44. Settling Time



$G = 1/2$

图 45. Large-Signal Step Response



$G = 2$

D046

图 46. Large-Signal Step Response

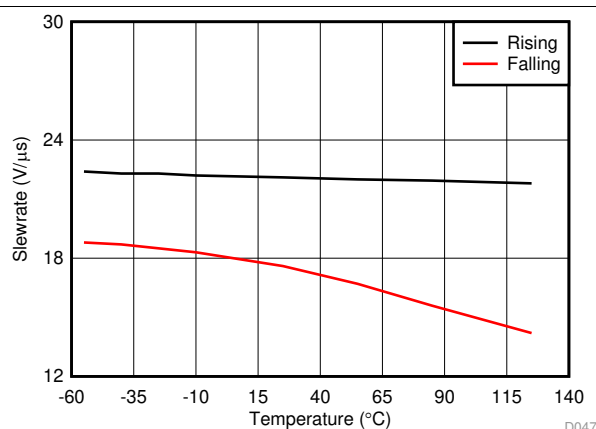


图 47. Slew Rate Over Temperature

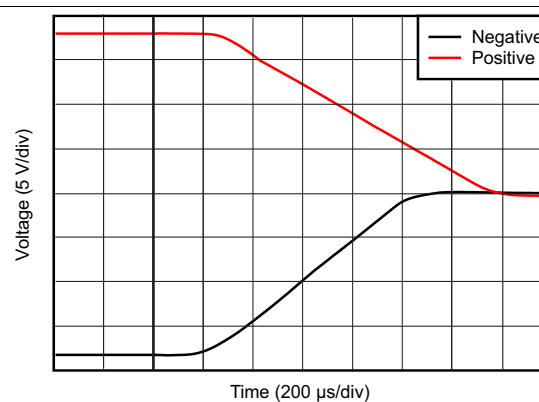
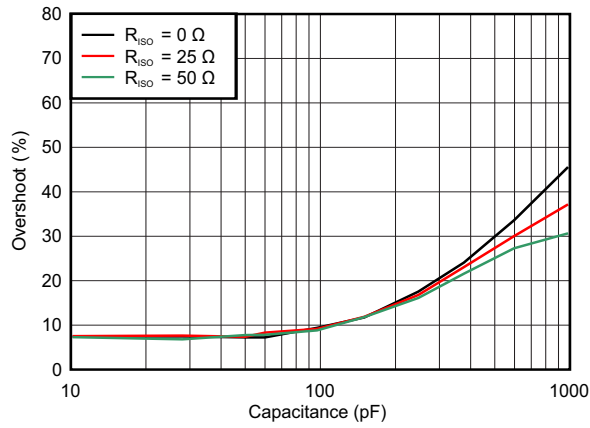


图 48. Overload Recovery (Normalized to 0 V)

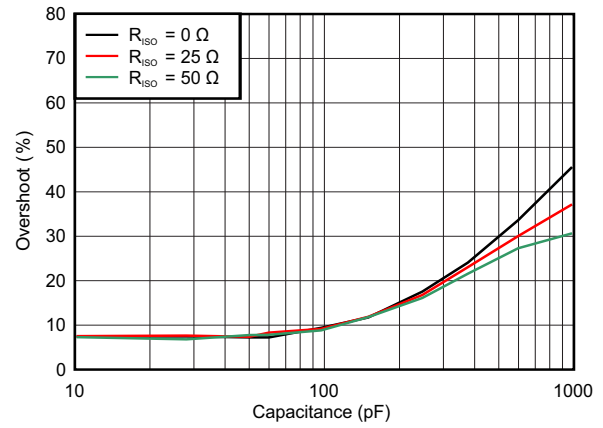
Typical Characteristics (接下页)

at $T_A = 25^\circ\text{C}$, $V_S = \pm 18\text{ V}$, $V_{CM} = V_{OUT} = V_S / 2$, $R_L = 10\text{ k}\Omega$, REF pin connected to ground, $G = 1/2$ (unless otherwise noted)



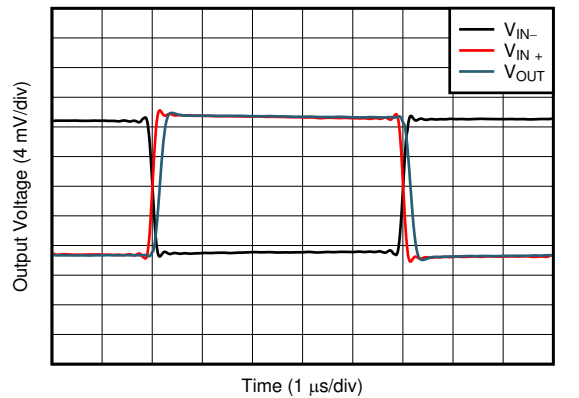
$G = 1/2$

图 49. Small-Signal Overshoot vs Capacitive Load



$G = 2$

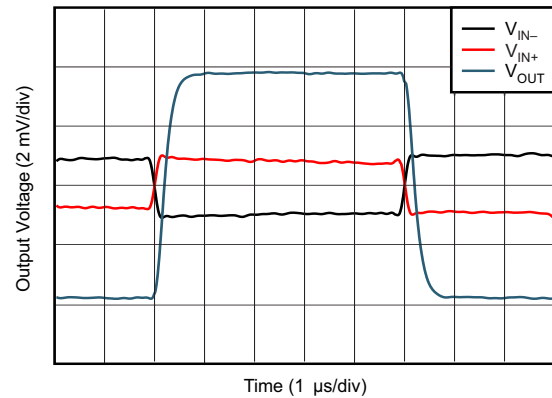
图 50. Small-Signal Overshoot vs Capacitive Load



$G = 1/2$

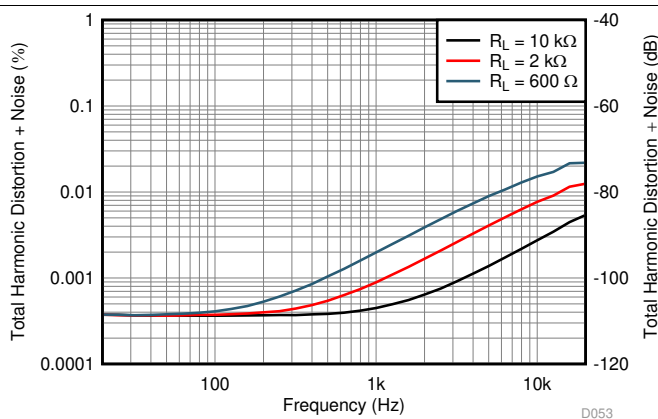
D051

图 51. Small-Signal Step Response



$G = 2$

图 52. Small-Signal Step Response

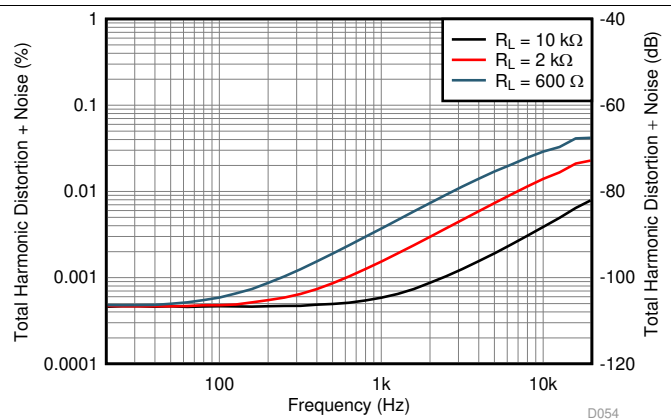


$G = 1/2$

$V_{OUT} = 3.5\text{ V}_{RMS}$

D053

图 53. THD+N vs Frequency



$G = 2$

$V_{OUT} = 3.5\text{ V}_{RMS}$

D054

图 54. THD+N vs Frequency

Typical Characteristics (接下页)

at $T_A = 25^\circ\text{C}$, $V_S = \pm 18\text{ V}$, $V_{CM} = V_{OUT} = V_S / 2$, $R_L = 10\text{ k}\Omega$, REF pin connected to ground, $G = 1/2$ (unless otherwise noted)

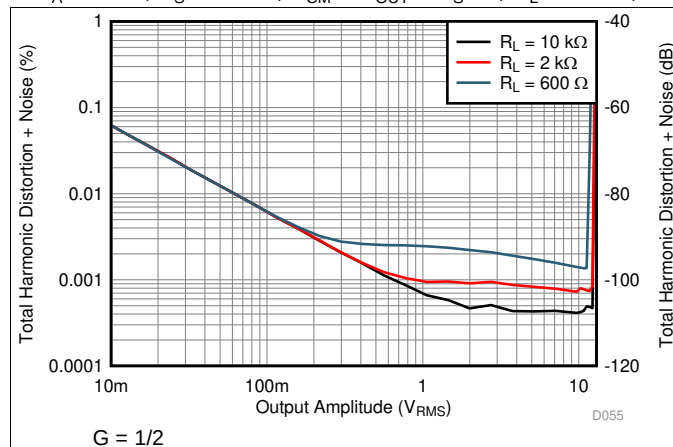


图 55. THD+N Ratio vs Output Amplitude

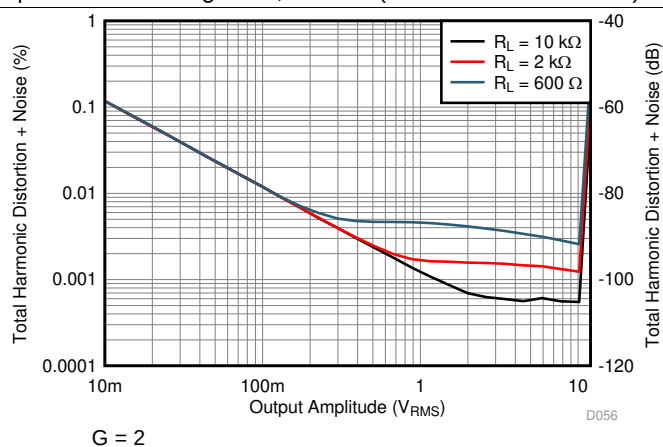


图 56. THD+N Ratio vs Output Amplitude

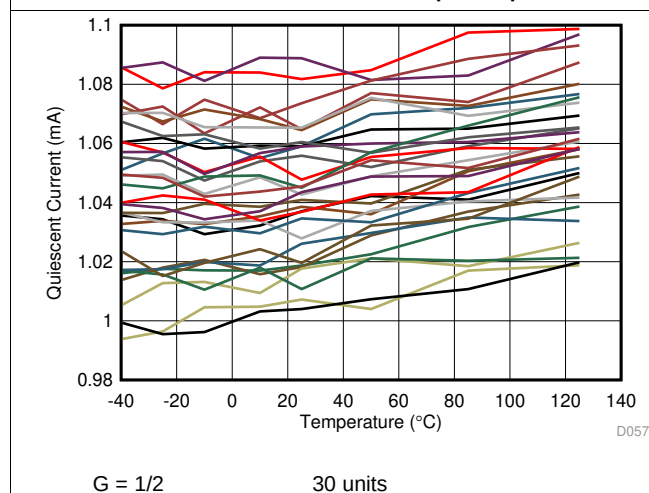


图 57. Supply Current vs Temperature

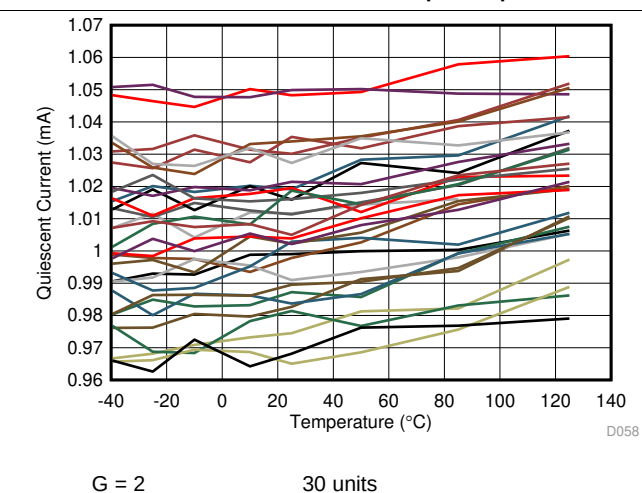


图 58. Supply Current vs Temperature

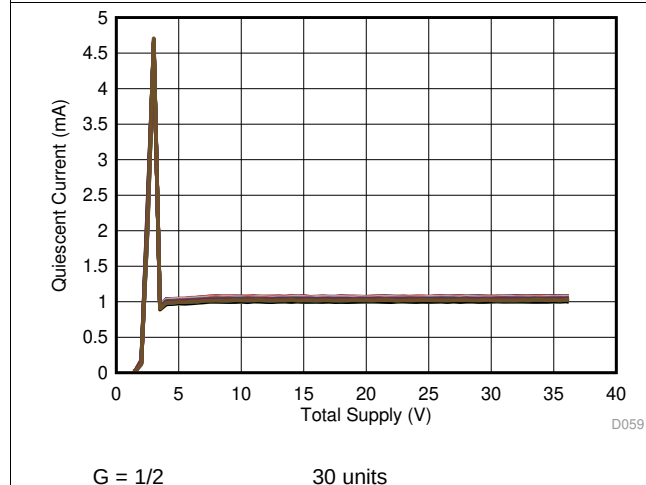


图 59. Supply Current vs Supply Voltage

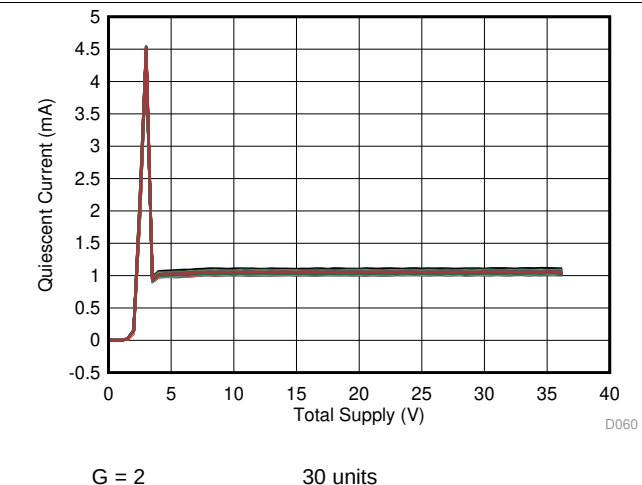
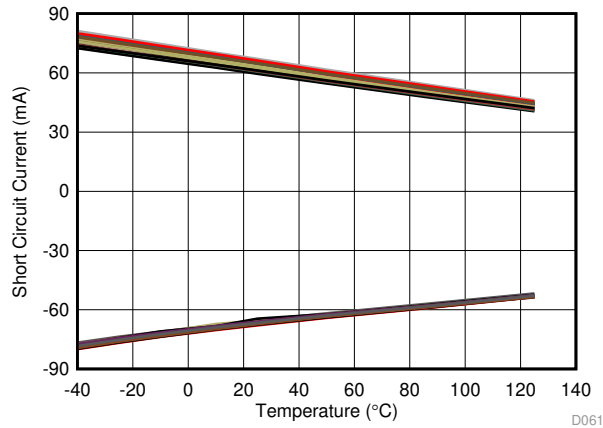


图 60. Supply Current vs Supply Voltage

Typical Characteristics (接下页)

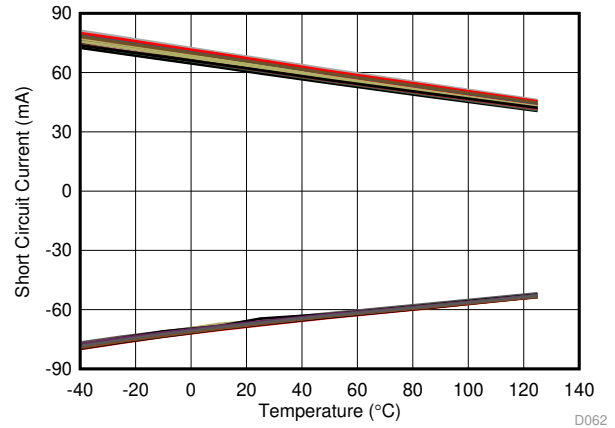
at $T_A = 25^\circ\text{C}$, $V_S = \pm 18\text{ V}$, $V_{CM} = V_{OUT} = V_S / 2$, $R_L = 10\text{ k}\Omega$, REF pin connected to ground, $G = 1/2$ (unless otherwise noted)



$G = 1/2$

30 units

图 61. Short Circuit Current vs Temperature



$G = 2$

30 units

图 62. Short Circuit Current vs Temperature

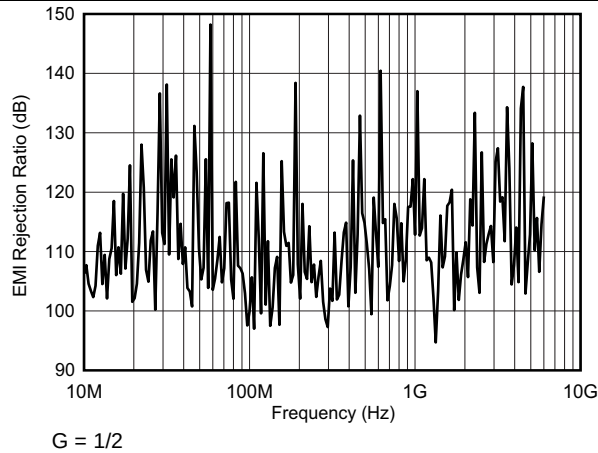


图 63. Differential-Mode EMI Rejection Ratio

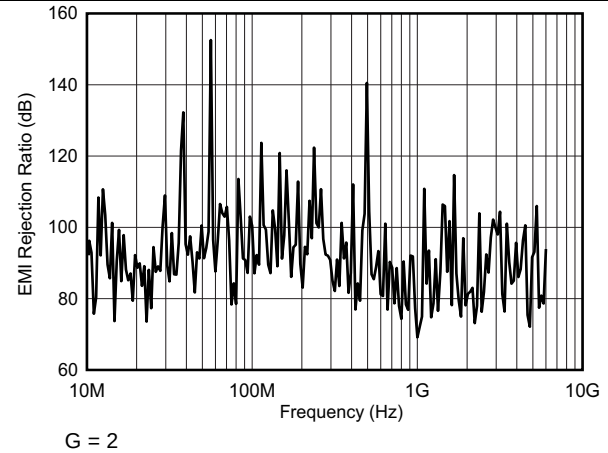


图 64. Differential-Mode EMI Rejection Ratio

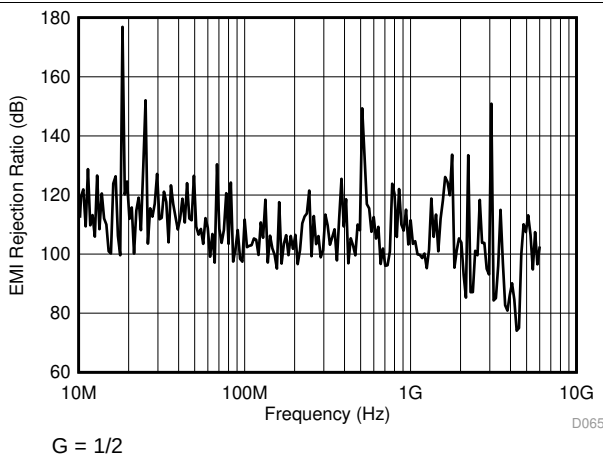


图 65. Common-Mode EMI Rejection Ratio

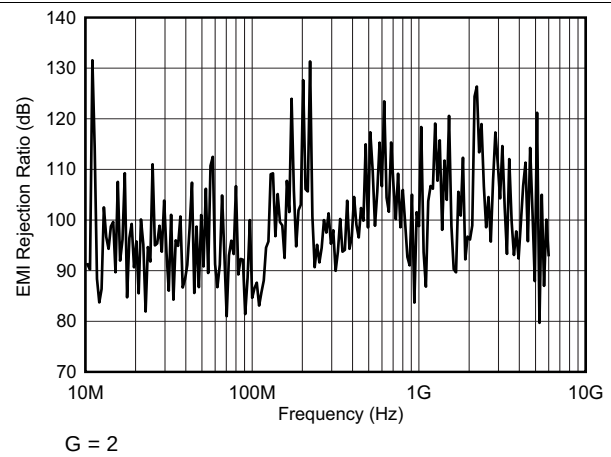
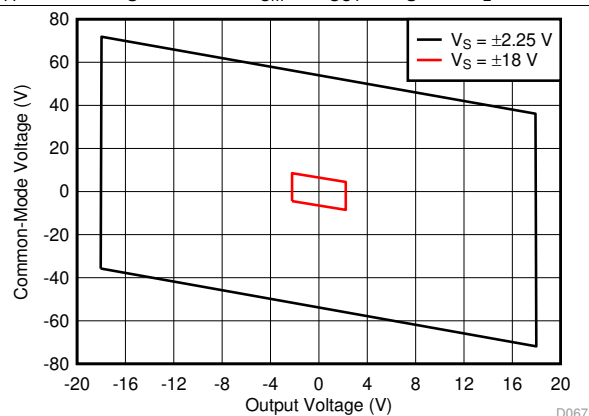


图 66. Common-Mode EMI Rejection Ratio

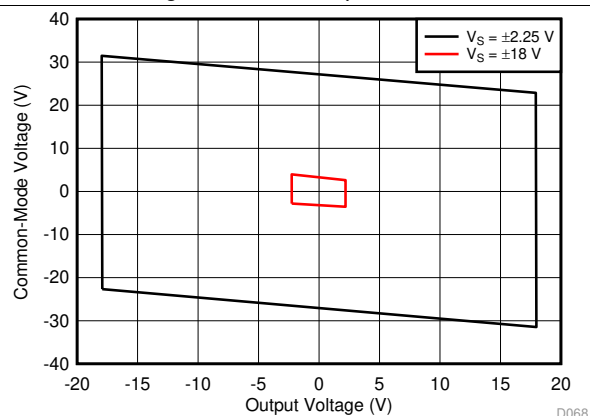
Typical Characteristics (接下页)

at $T_A = 25^\circ\text{C}$, $V_S = \pm 18\text{ V}$, $V_{CM} = V_{OUT} = V_S / 2$, $R_L = 10\text{ k}\Omega$, REF pin connected to ground, $G = 1/2$ (unless otherwise noted)



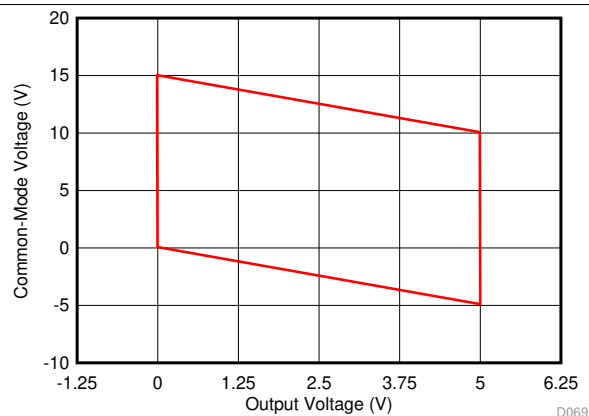
$G = 1/2$ Bipolar supply $V_{REF} = 0\text{ V}$

图 67. Input Common-Mode Voltage vs Output Voltage



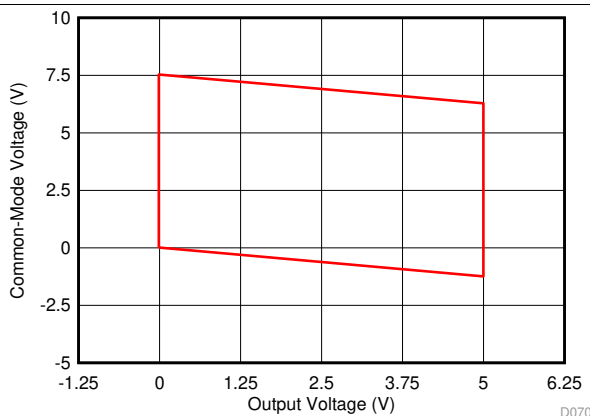
$G = 2$ Bipolar supply $V_{REF} = 0\text{ V}$

图 68. Input Common-Mode Voltage vs Output Voltage



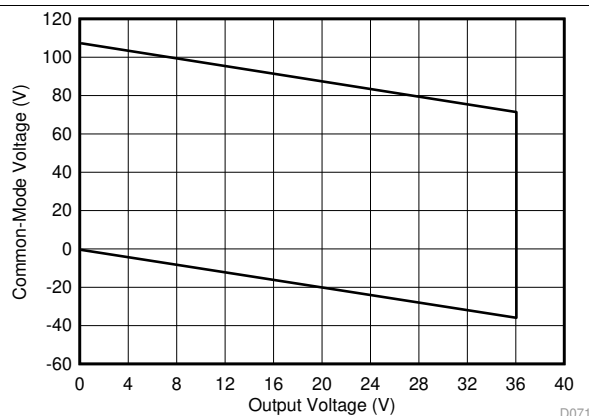
$G = 1/2$ 5-V supply $V_{REF} = 0\text{ V}$

图 69. Input Common-Mode Voltage vs Output Voltage



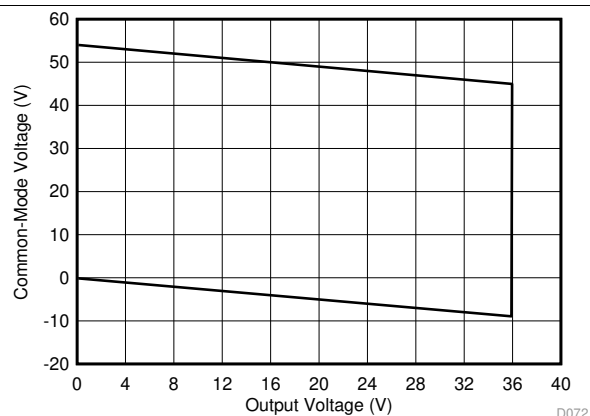
$G = 2$ 5-V supply $V_{REF} = 0\text{ V}$

图 70. Input Common-Mode Voltage vs Output Voltage ,



$G = 1/2$ 36-V supply $V_{REF} = 0\text{ V}$

图 71. Input Common-Mode Voltage vs Output Voltage



$G = 2$ 36-V supply $V_{REF} = 0\text{ V}$

图 72. Input Common-Mode Voltage vs Output Voltage

Typical Characteristics (接下页)

at $T_A = 25^\circ\text{C}$, $V_S = \pm 18\text{ V}$, $V_{CM} = V_{OUT} = V_S / 2$, $R_L = 10\text{ k}\Omega$, REF pin connected to ground, $G = 1/2$ (unless otherwise noted)

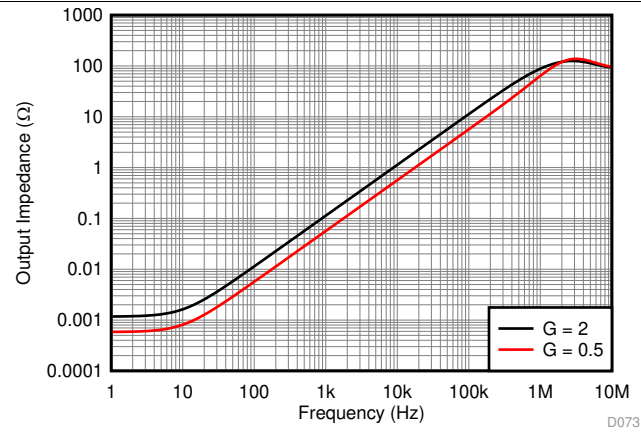


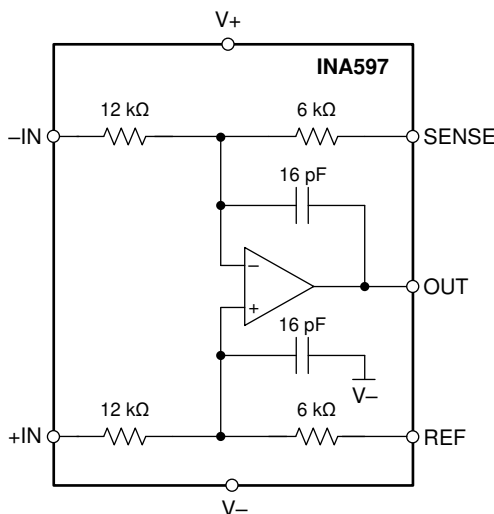
图 73. Closed-Loop Output Impedance vs Frequency

8 Detailed Description

8.1 Overview

The INA597 consists of a high-precision, e-trim™ operational amplifier and four trimmed resistors. These resistors can be connected to make a wide variety of amplifier configurations, including difference, noninverting, and inverting configurations. Using the on-chip resistors of the INA597 provides the designer with several advantages over a discrete design. The INA597 also includes internal compensation capacitors, as shown in [Functional Block Diagram](#).

8.2 Functional Block Diagram



8.3 Feature Description

Much of the dc performance of op-amp circuits depends on the accuracy of the surrounding resistors. The resistors on the INA597 are laid out to be tightly matched. The resistors of each part are matched on-chip and tested for their matching accuracy. As a result of this trimming and testing, the INA597 provides high accuracy for specifications such as gain drift, common-mode rejection, and gain error.

8.4 Device Functional Modes

The INA597 measures voltages beyond the rails. For the $G = \frac{1}{2}$ and $G = 2$ difference amplifier configurations, see the input voltage range in the [Specifications](#) section for details. The INA597 can be configured in several ways; see [Figure 78](#) to [Figure 82](#). These configurations rely on the internal, matched resistors; therefore, all of these configurations have excellent gain accuracy and gain drift.

9 Application and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

图 74 shows the basic connections required for operation of the INA597. Connect power supply bypass capacitors close to the device pins.

The differential input signal is connected to pins 2 and 3, as shown. The source impedances connected to the inputs must be nearly equal to provide good common-mode rejection. An 8-Ω mismatch in source impedance degrades the common-mode rejection of a typical device to approximately 80 dB. Gain accuracy is also slightly affected. If the source has a known impedance mismatch, use an additional resistor in series with one input to preserve good common-mode rejection.

9.2 Typical Applications

9.2.1 Basic Power-Supply and Signal Connections

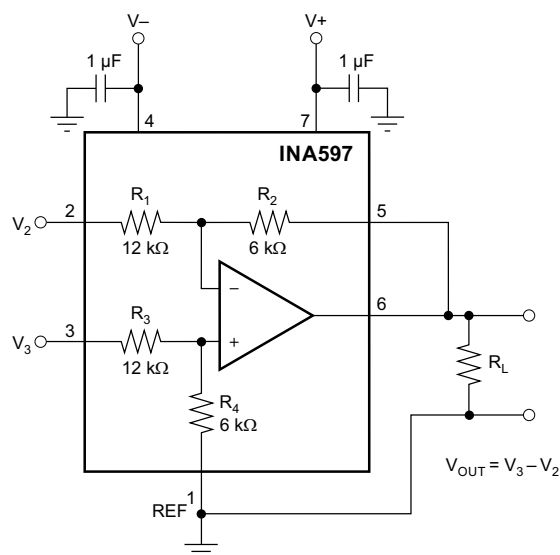


图 74. Basic Power-Supply and Signal Connections

9.2.1.1 Design Requirements

For the application shown in 图 74, the design requirements are:

- Gain of $G = \frac{1}{2}$
- $V_{REF} = 0 \text{ V}$

Typical Applications (接下页)

9.2.1.2 Detailed Design Procedure

9.2.1.2.1 Operating Voltage

The INA597 operates from single (4.5 V to 36 V) or dual (± 2.25 V to ± 18 V) supplies with excellent performance. Specifications are production tested with +5-V and ± 15 -V supplies. Most behavior remains unchanged throughout the full operating voltage range. Parameters that vary significantly with operating voltage are shown in the [Typical Characteristics](#). The internal op amp in the INA597 is a single-supply design. This design allows linear operation with the op amp common-mode voltage equal to, or slightly less than V_- (or single-supply ground). Although input voltages on pins 2 and 3 that are less than the negative supply voltage do not damage the device, operation in this region is not recommended. Transient conditions at the inverting input terminal less than the negative supply can cause a positive feedback condition that could lock the device output to the negative rail.

The INA597 accurately measures differential signals that are greater than the positive power supply. For example with $G = \frac{1}{2}$, the linear common-mode range extends to nearly three times the positive power supply voltage; see the [Typical Characteristics](#) as well as the [Input Voltage Range](#) sections.

9.2.1.2.2 Offset Voltage Trim

The INA597 is production trimmed for low offset voltage and drift. Most applications require no external offset adjustment. 图 75 shows an optional circuit for trimming the output offset voltage. The output is referred to the output reference terminal (pin 1), which is normally grounded. A voltage applied to the REF pin is summed with the output signal. This configuration can be used to null offset voltage. To maintain good common-mode rejection, make sure the source impedance of a signal applied to the REF pin is less than $8\ \Omega$. For low impedance at the REF pin, the trim voltage can be buffered with an op amp, such as the [OPA177](#).

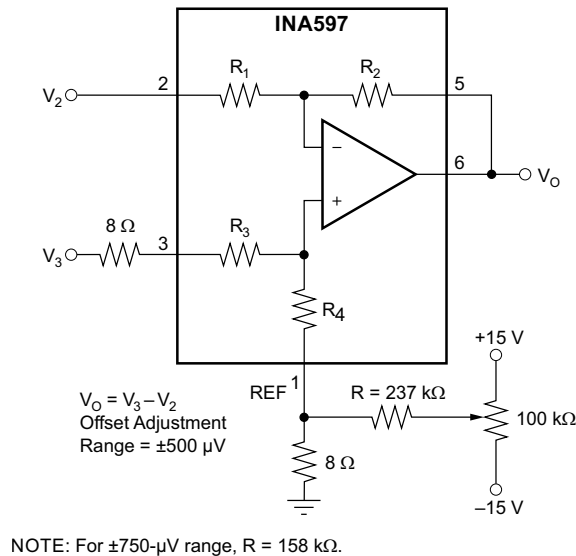


图 75. Offset Adjustment

Typical Applications (接下页)

9.2.1.2.3 Input Voltage Range

The INA597 measures input voltages beyond the supply rails. The internal resistors divide down the voltage before the voltage reaches the internal op amp and provide protection to the op amp inputs. 图 76 shows an example of how the voltage division works in a difference-amplifier configuration. For the INA597 to measure correctly, the input voltages at the input nodes of the internal op amp must stay less than 0.1 V of the positive supply rail, and can exceed the negative supply rail by 0.1 V. Refer to the [Power Supply Recommendations](#) section for more details.

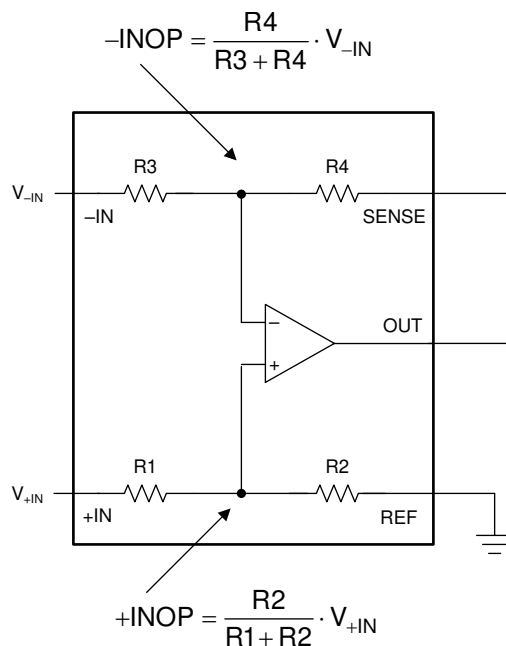


图 76. Voltage Division in the Difference Amplifier Configuration

The INA597 has integrated ESD diodes at the inputs that provide overvoltage protection. This feature simplifies system design by eliminating the need for additional external protection circuitry, and enables a more robust system. The voltages at any of the inputs of the parts in $G = \frac{1}{2}$ configuration with ± 18 V supplies can safely range from $+V_S - 54$ V up to $-V_S + 54$ V. For example, on ± 10 -V supplies, the input voltages can go as high as ± 30 V.

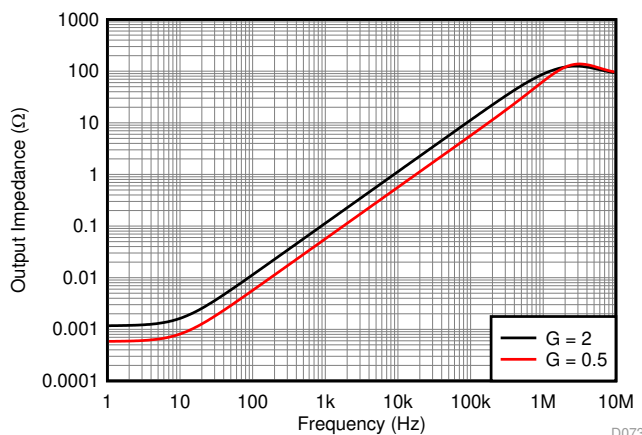
9.2.1.2.4 Capacitive Load Drive Capability

The INA597 can drive large capacitive loads, even at low supplies. The device is stable with a 500-pF load. Refer to the [Typical Characteristics](#).

Typical Applications (接下页)

9.2.1.3 Application Curve

The interaction between the output stage of an operational amplifier (op amp) and capacitive loads can impact the stability of the circuit. Throughout the industry, op-amp output-stage requirements have changed greatly since their original creation. Classic output stages with the class-AB common-emitter bipolar junction transistor (BJT) have now been replaced with common-collector BJT and common-drain complementary metal-oxide semiconductor (CMOS) devices. Both of these technologies enable rail-to-rail output voltages for single-supply and battery-powered applications. A result of changing these output-stage structures is that the op-amp open-loop output impedance (Z_o) changed from the largely resistive behavior of early BJT op amps to a frequency-dependent Z_o that features capacitive, resistive, and inductive portions. Proper understanding of Z_o over frequency—and also the resulting closed-loop output impedance over frequency—is crucial for the understanding of loop gain, bandwidth, and stability analysis. 图 77 shows the INA597 closed-loop output impedance, and how it varies over frequency.



$$V_S = \pm 18 \text{ V}$$

图 77. Closed-Loop Output Impedance vs Frequency

Typical Applications (接下页)

9.2.2 Precision Instrumentation Amplifier

The INA597 can be combined with op amps to form a complete instrumentation amplifier (IA) with specialized performance characteristics, as shown in 图 78.

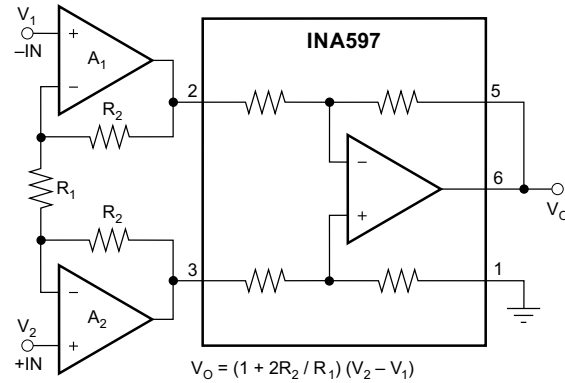


图 78. Precision Instrumentation Amplifier

9.2.3 Low Power, High-Output Current, Precision, Difference Amplifier

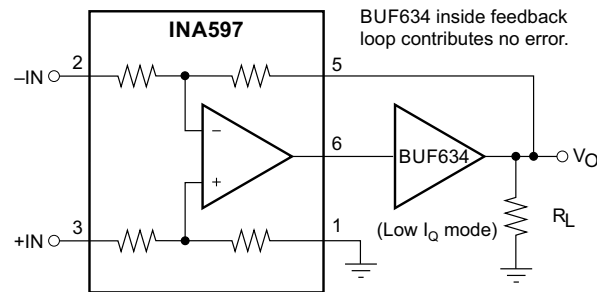


图 79. Low Power, High-Output Current, Precision, Difference Amplifier

9.2.4 Pseudoground Generator

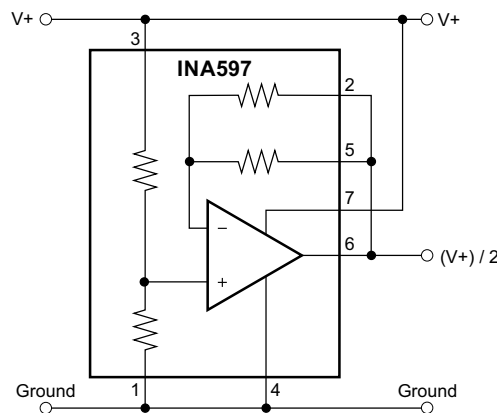


图 80. Pseudoground Generator

Typical Applications (接下页)

9.2.7 Additional Applications

Texas Instruments offers many complete high-performance instrumentation amplifiers. See [表 2](#) for some of the products with related performance.

表 2. Recommendations for Op Amp Products to be Used With the INA597

A1, A2	FEATURE	SIMILAR TI IA
OPA27	Low noise	INA103
OPA129	Ultra-low bias current (fA)	INA116
OPA177	Low offset drift, low noise	INA114 , INA128
OPA2130	Low power, FET-input (pA)	INA111
OPA2234	Single supply, precision, low power	INA122 , INA118
OPA2237	Single supply, low power, 8-pin MSOP	INA122 , INA126

The difference amplifier is a highly versatile building block that is useful in a wide variety of applications. See the [INA105 data sheet](#) for additional applications ideas, including:

- Current Receiver With Compliance to Rails
- Precision Unity-Gain Inverting Amplifier
- ± 10 -V Precision Voltage Reference
- ± 5 -V Precision Voltage Reference
- Precision Unity-Gain Buffer
- Precision Average Value Amplifier
- Precision $G = 2$ Amplifier
- Precision Summing Amplifier
- Precision $G = 1/2$ Amplifier
- Precision Bipolar Offsetting
- Precision Summing Amplifier With Gain
- Instrumentation Amplifier Guard Drive Generator
- Precision Summing Instrumentation Amplifier
- Precision Absolute Value Buffer
- Precision Voltage-to-Current Converter With Differential Inputs
- Differential Input Voltage-to-Current Converter for Low IOUT
- Isolating Current Source
- Differential Output Difference Amplifier
- Isolating Current Source With Buffering Amplifier for Greater Accuracy
- Window Comparator With Window Span and Window Center Inputs
- Precision Voltage-Controlled Current Source With Buffered Differential Inputs and Gain
- Digitally Controlled Gain of ± 1 Amplifier

10 Power Supply Recommendations

The nominal performance of the INA597 is specified with a supply voltage of ± 15 V and midsupply reference voltage. The device operates using power supplies from ± 2.25 V (4.5 V) to ± 18 V (36 V) and non-midsupply reference voltages with excellent performance. Parameters that can vary significantly with operating voltage and reference voltage are shown in the [Typical Characteristics](#).

11 Layout

11.1 Layout Guidelines

Attention to good layout practices is always recommended. For best operational performance of the device, use good PCB layout practices, including:

- Take care to make sure that both input paths are well-matched for source impedance and capacitance to avoid converting common-mode signals into differential signals.
- Noise propagates into analog circuitry through the power pins of the circuit as a whole and of the device. Bypass capacitors reduce the coupled noise by providing low-impedance power sources local to the analog circuitry.
 - Connect low-ESR, 0.1- μ F ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is applicable for single-supply applications.
- To reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If these traces cannot be kept separate, crossing the sensitive trace perpendicular is much better than in parallel with the noisy trace.
- Place the external components as close to the device as possible.
- Keep the traces as short as possible.

11.2 Layout Example

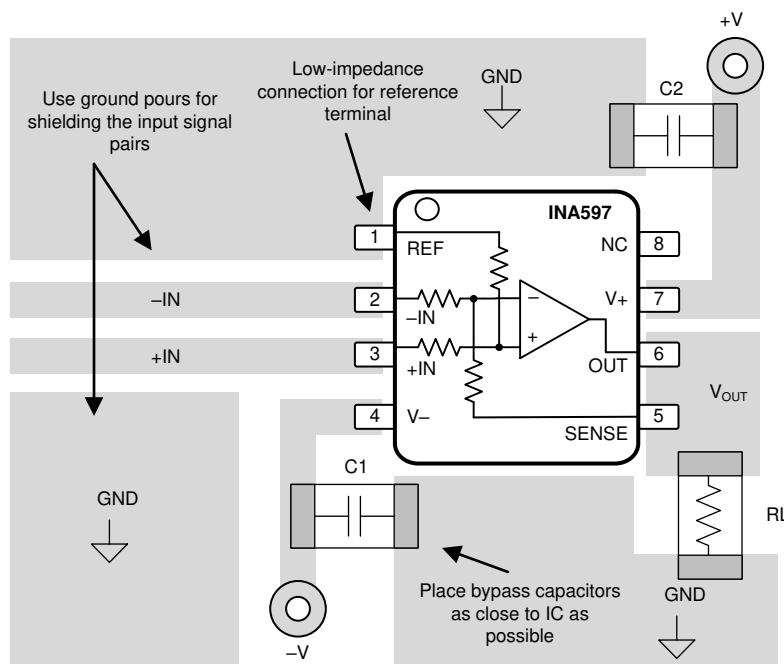
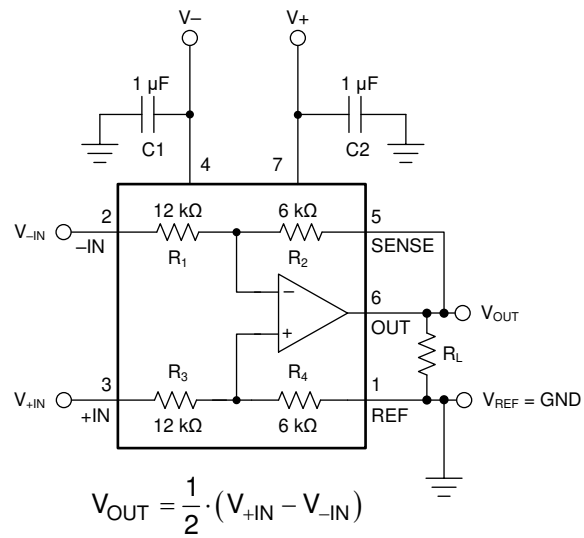


图 83. Example Schematic and Associated PCB Layout

12 器件和文档支持

12.1 文档支持

12.1.1 相关文档

请参阅如下相关文档：

- 德州仪器 (TI)，《通用差分放大器评估模块》用户指南
- 德州仪器 (TI)，《适用于电机控制位置反馈的精密信号调节解决方案》技术简介

12.2 接收文档更新通知

要接收文档更新通知，请导航至 TI.com.cn 上的器件产品文件夹。单击右上角的通知我 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

12.3 支持资源

[TI E2E™ support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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12.4 商标

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12.5 静电放电警告



ESD 可能会损坏该集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理措施和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

12.6 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更，恕不另行通知，且不会对此文档进行修订。如需获取此数据表的浏览器版本，请查阅左侧的导航栏。

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
INA597IDGKR	ACTIVE	VSSOP	DGK	8	2500	RoHS & Green	NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	1WT6	Samples
INA597IDGKT	ACTIVE	VSSOP	DGK	8	250	RoHS & Green	NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	1WT6	Samples
INA597IDR	ACTIVE	SOIC	D	8	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR		INA597	Samples
INA597IDRCR	ACTIVE	VSON	DRC	10	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	IN597	Samples
INA597IDRCT	ACTIVE	VSON	DRC	10	250	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	IN597	Samples
INA597IDT	ACTIVE	SOIC	D	8	250	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR		INA597	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

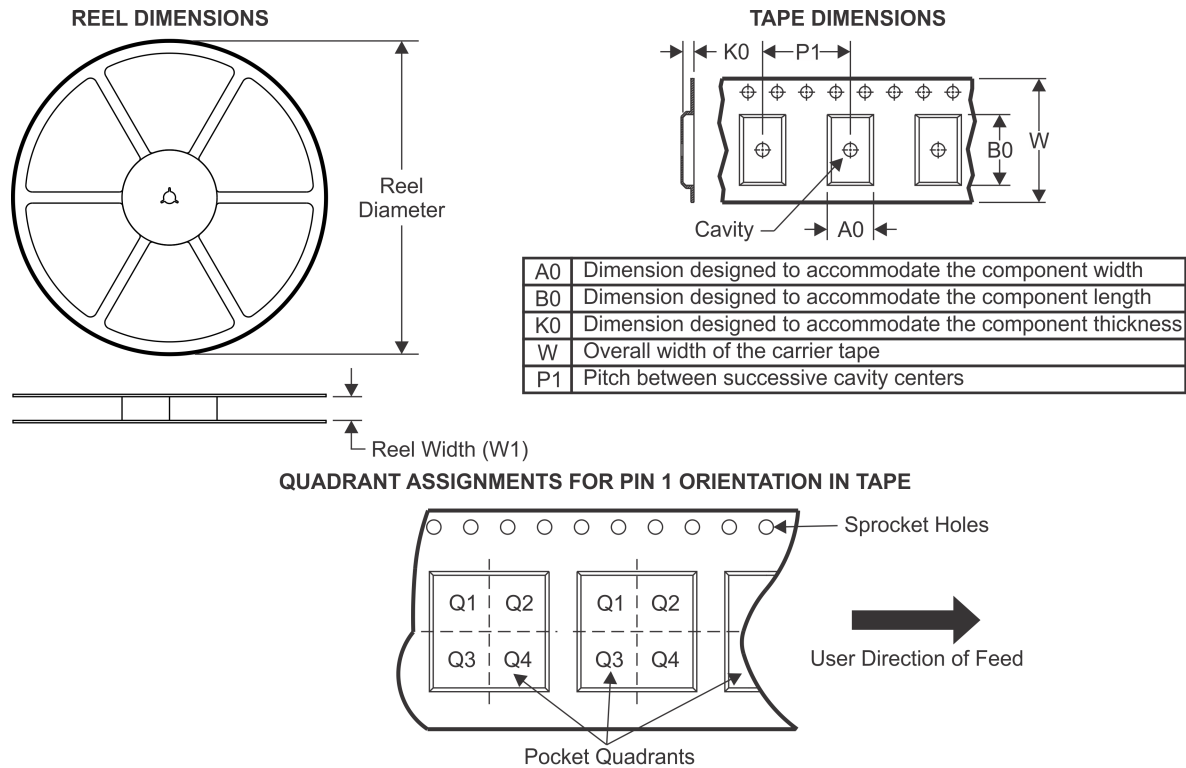
(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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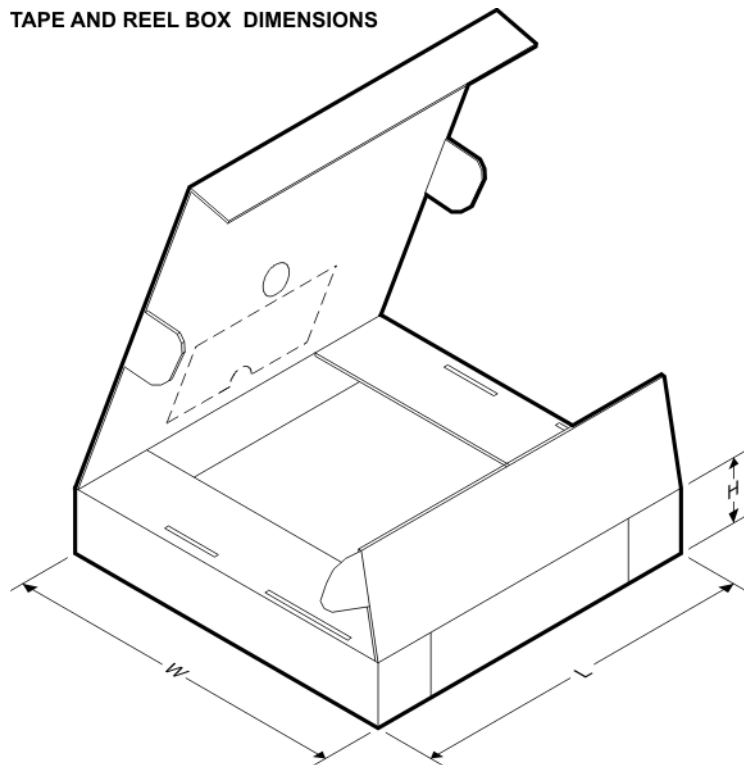
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
INA597IDGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
INA597IDGKT	VSSOP	DGK	8	250	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
INA597IDR	SOIC	D	8	3000	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
INA597IDRCR	VSON	DRC	10	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
INA597IDRCT	VSON	DRC	10	250	180.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
INA597IDT	SOIC	D	8	250	180.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS

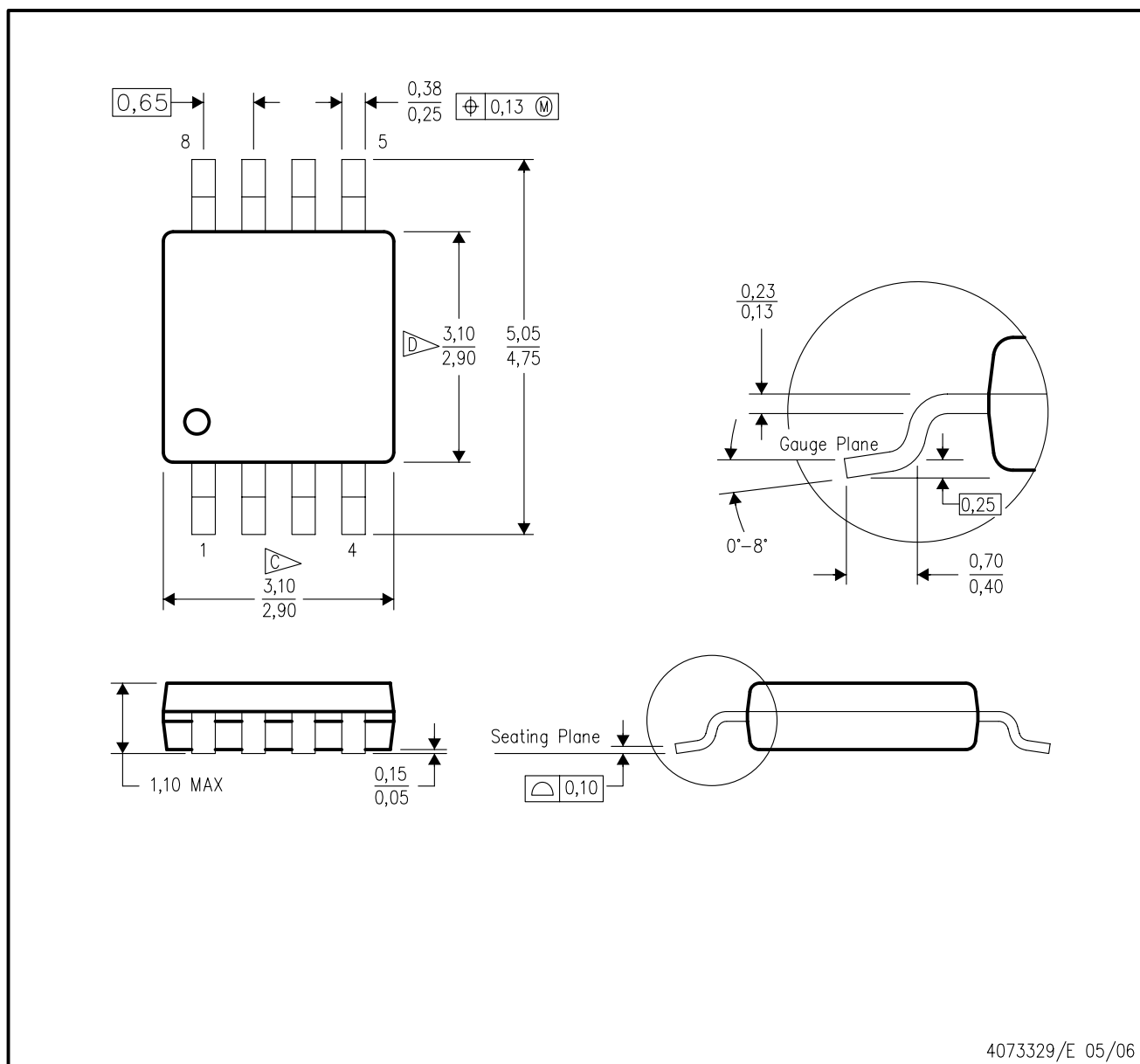


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
INA597IDGKR	VSSOP	DGK	8	2500	366.0	364.0	50.0
INA597IDGKT	VSSOP	DGK	8	250	366.0	364.0	50.0
INA597IDR	SOIC	D	8	3000	853.0	449.0	35.0
INA597IDRCR	VSON	DRC	10	3000	367.0	367.0	35.0
INA597IDRCT	VSON	DRC	10	250	210.0	185.0	35.0
INA597IDT	SOIC	D	8	250	210.0	185.0	35.0

DGK (S-PDSO-G8)

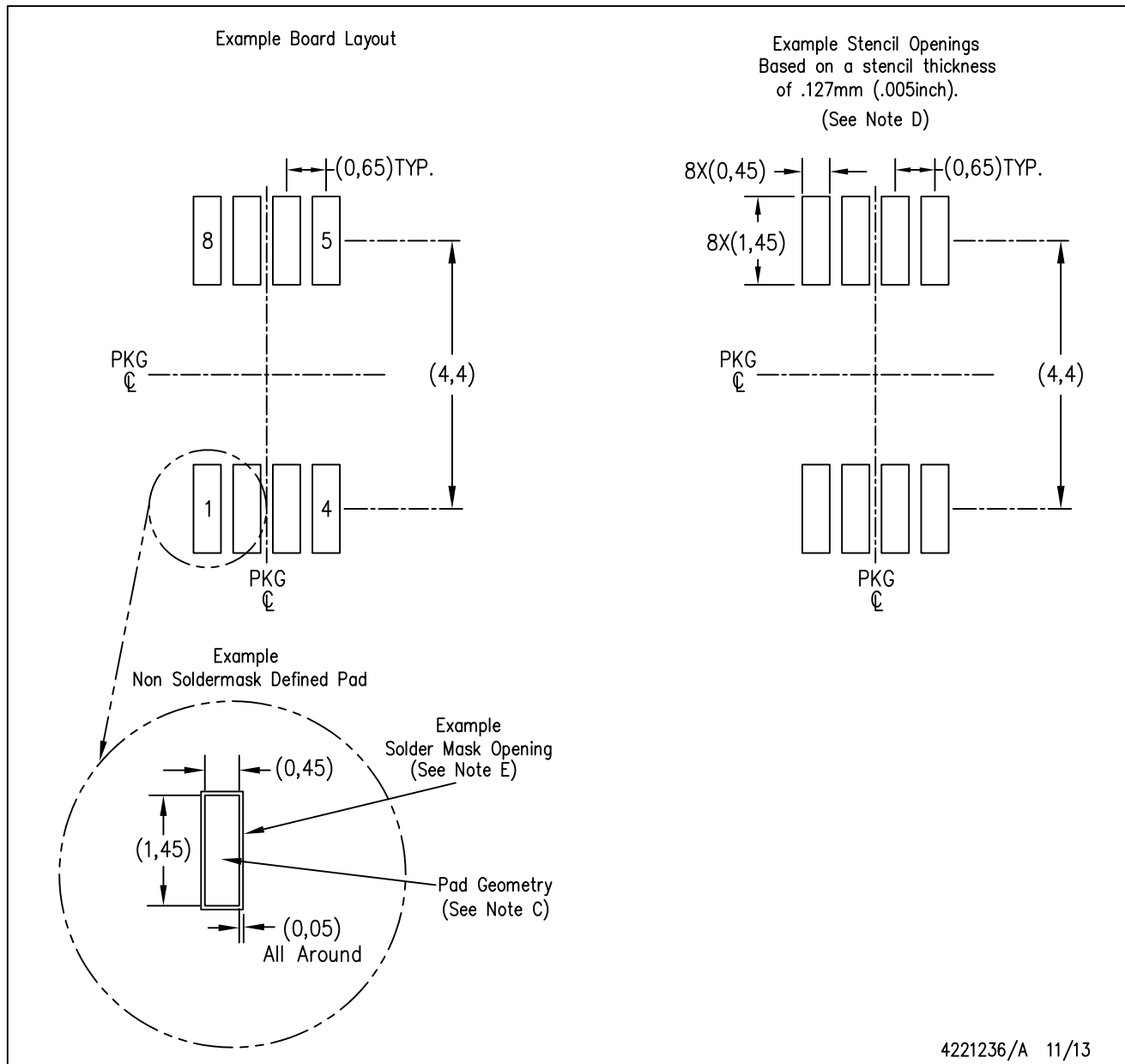
PLASTIC SMALL-OUTLINE PACKAGE



4073329/E 05/06

DGK (S-PDSO-G8)

PLASTIC SMALL OUTLINE PACKAGE



- NOTES:
- All linear dimensions are in millimeters.
 - This drawing is subject to change without notice.
 - Publication IPC-7351 is recommended for alternate designs.
 - Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
 - Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

GENERIC PACKAGE VIEW

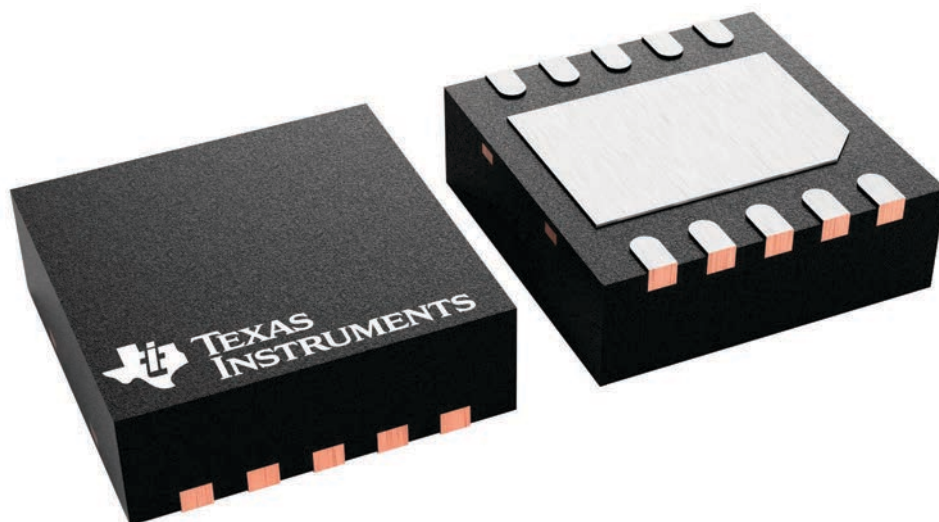
DRC 10

VSON - 1 mm max height

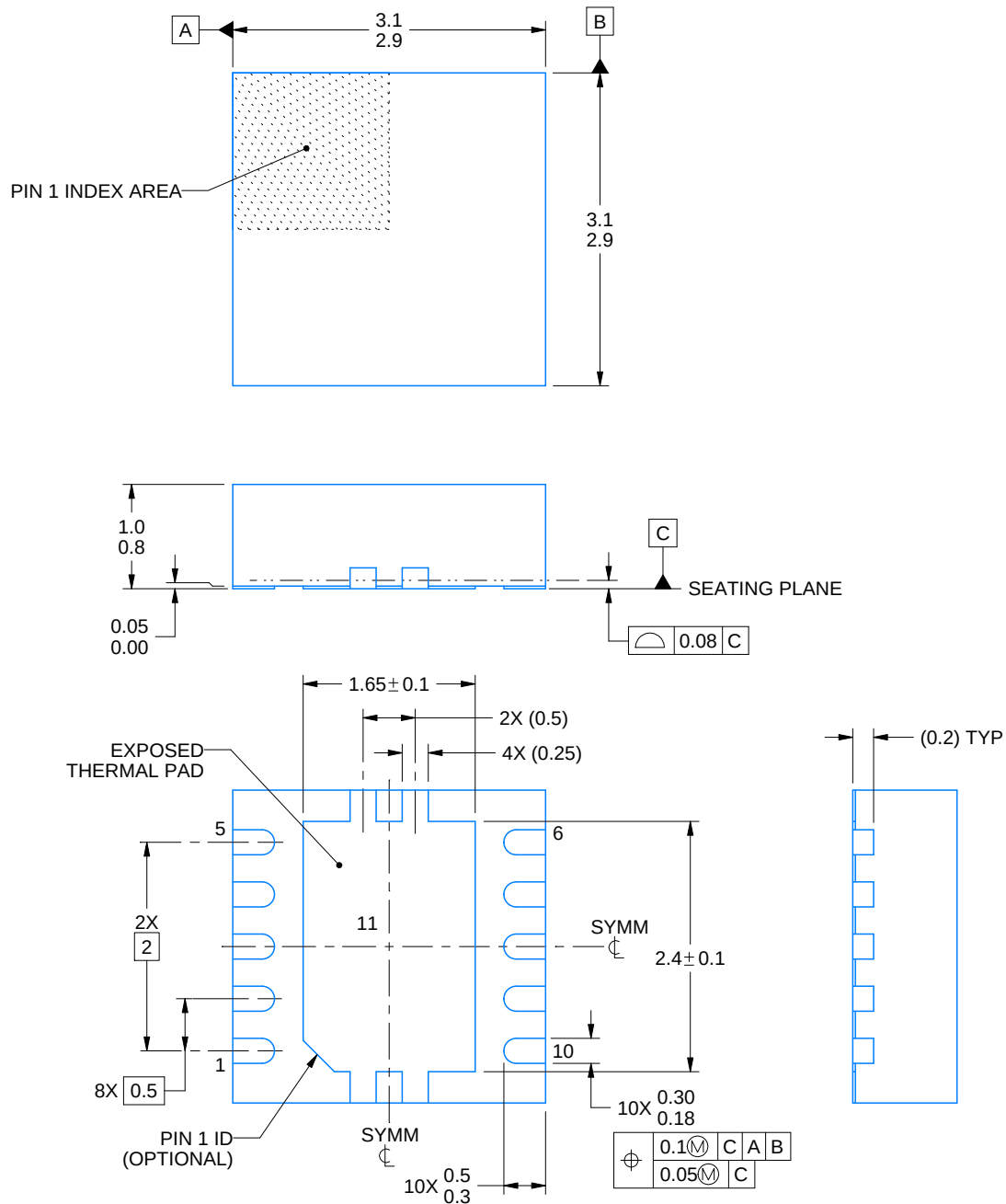
3 x 3, 0.5 mm pitch

PLASTIC SMALL OUTLINE - NO LEAD

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



4226193/A



4218878/B 07/2018

NOTES:

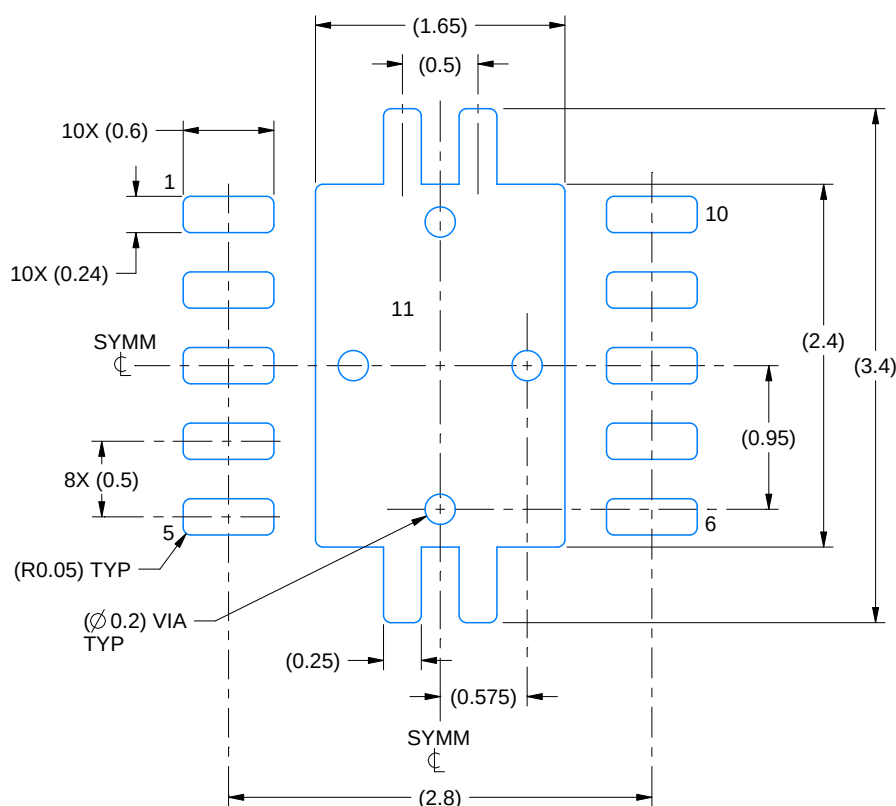
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.

EXAMPLE BOARD LAYOUT

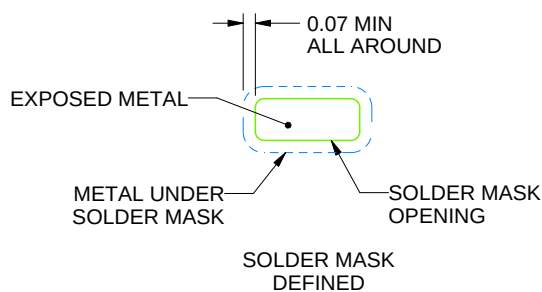
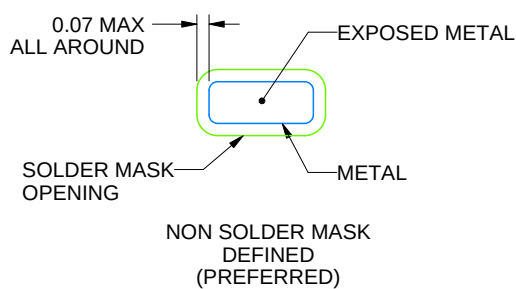
DRC0010J

VSON - 1 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:20X



SOLDER MASK DETAILS

4218878/B 07/2018

NOTES: (continued)

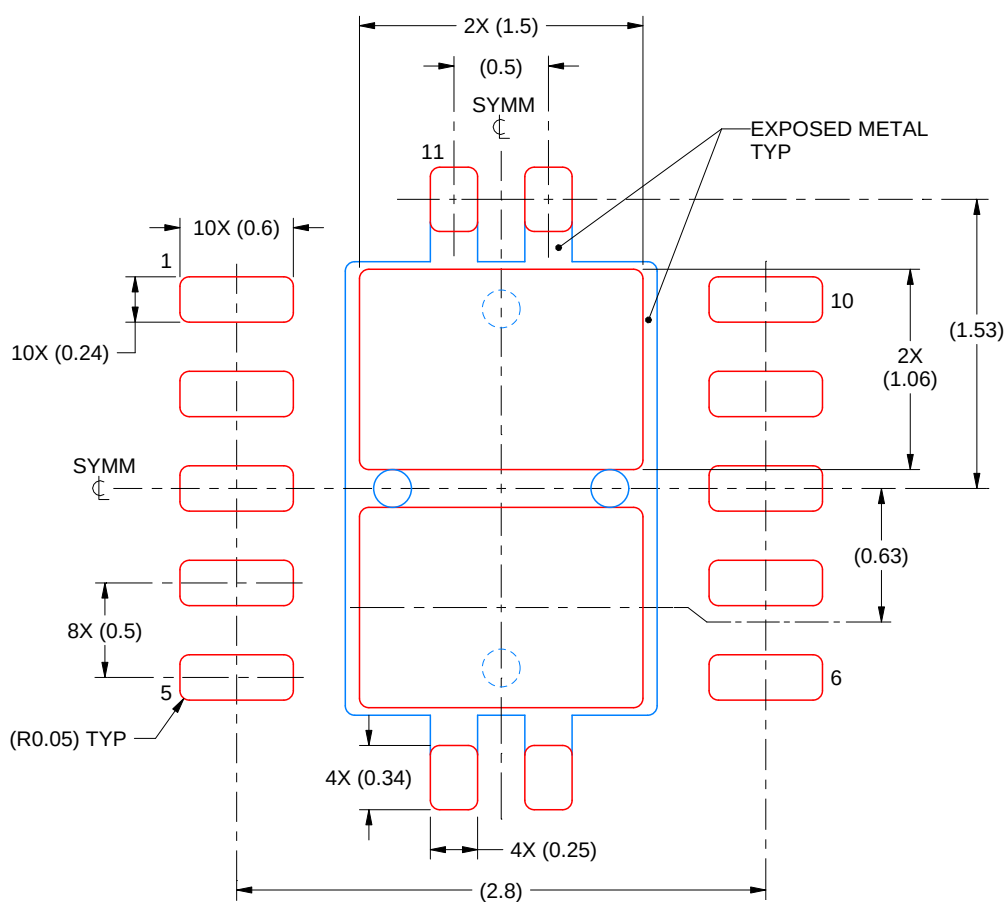
- This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/sluea271).
- Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

EXAMPLE STENCIL DESIGN

DRC0010J

VSON - 1 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



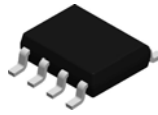
SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD 11:
80% PRINTED SOLDER COVERAGE BY AREA
SCALE:25X

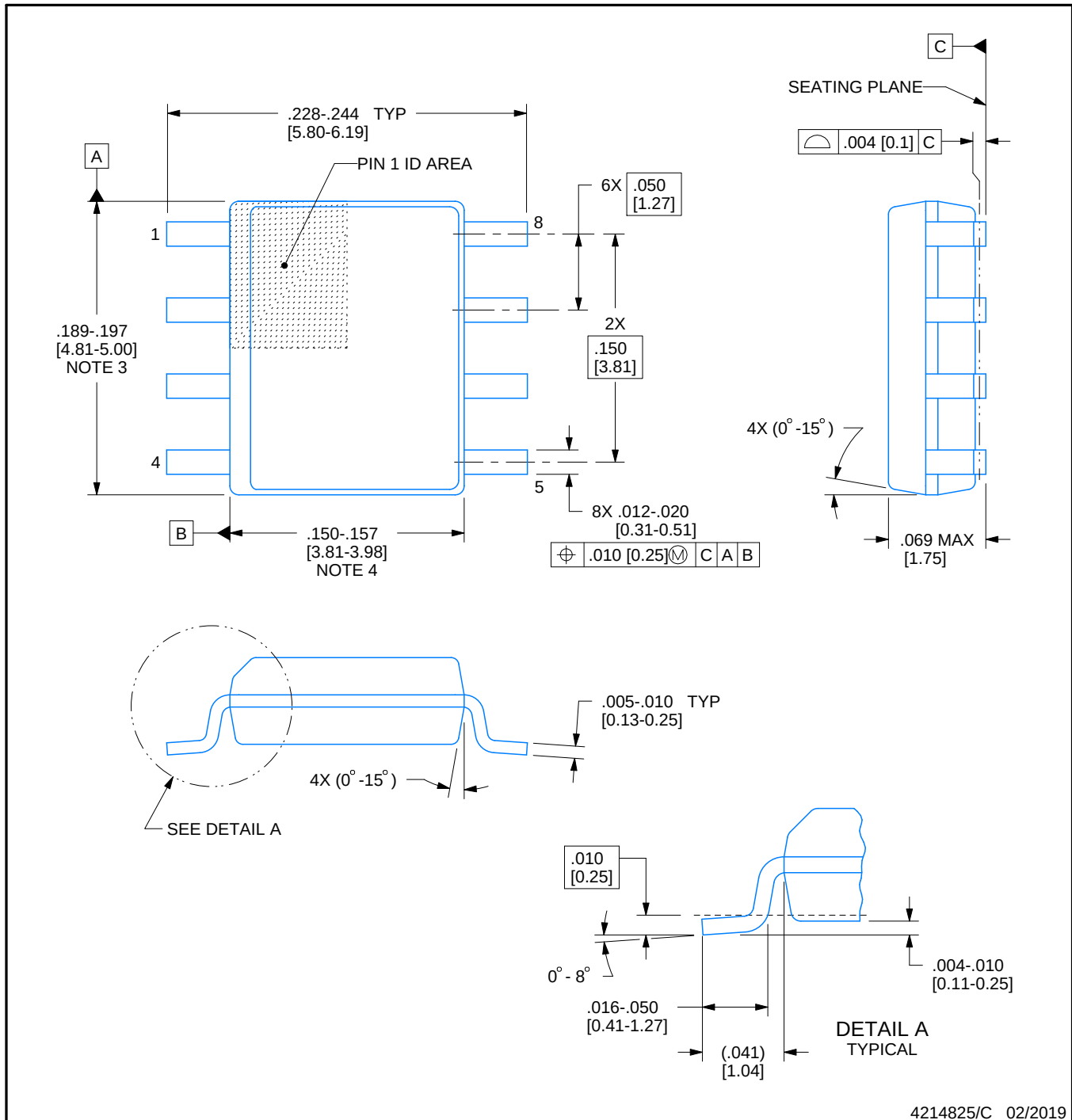
4218878/B 07/2018

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

D0008A**PACKAGE OUTLINE****SOIC - 1.75 mm max height**

SMALL OUTLINE INTEGRATED CIRCUIT



4214825/C 02/2019

NOTES:

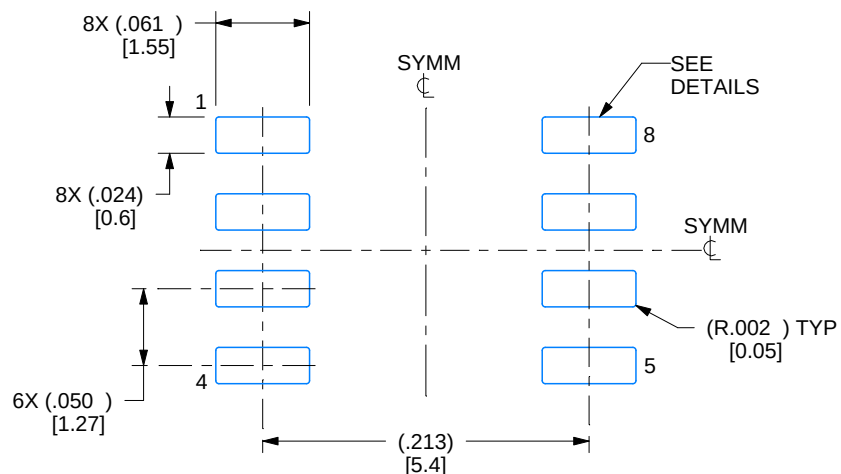
1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed $.006$ [0.15] per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MS-012, variation AA.

EXAMPLE BOARD LAYOUT

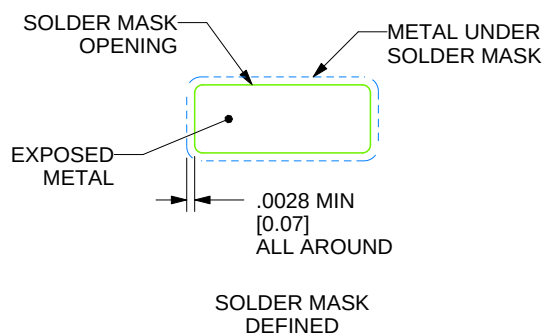
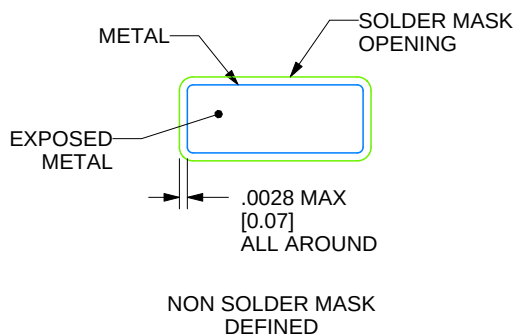
D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:8X



SOLDER MASK DETAILS

4214825/C 02/2019

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

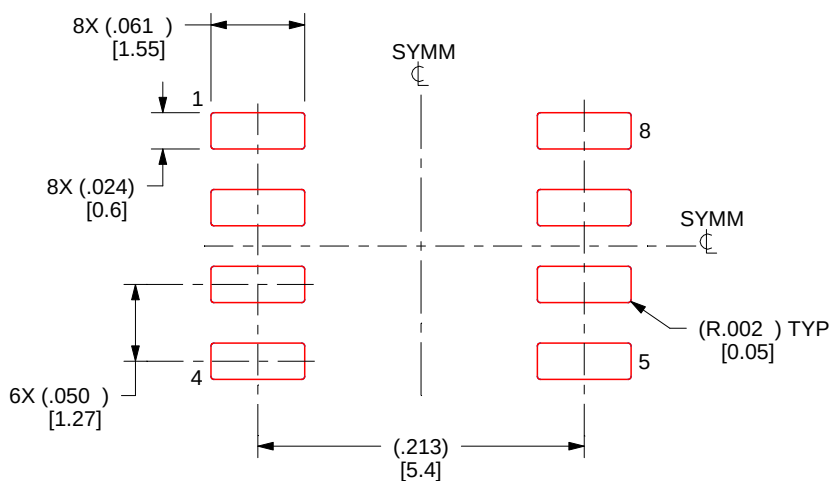
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE
BASED ON .005 INCH [0.125 MM] THICK STENCIL
SCALE:8X

4214825/C 02/2019

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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